

Overcoming Offset

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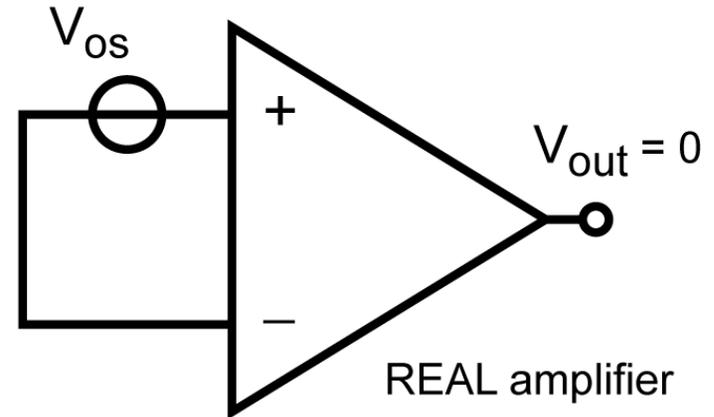
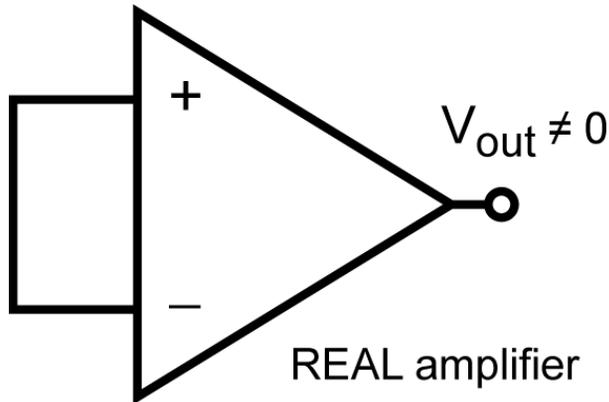
Motivation

- The offset of amplifiers realized in standard IC technologies is typically in the **millivolt** range
- However, many analog circuits e.g. opamps, comparators, ADCs and DACs require amplifiers with **microvolt** offsets
- Also, many sensors (e.g. thermopiles, bridges, hall-effect sensors etc.) output DC signals that need to be processed with **microvolt** precision
- This tutorial will focus on **dynamic** offset-cancellation (DOC) techniques, with which offset can be reduced to the **microvolt** level.

Outline

- Differential amplifiers
 - Offset and $1/f$ noise
- Dynamic Offset Cancellation (DOC)
 - Auto-zeroing
 - Correlated Double-Sampling (CDS)
 - Chopping
- Summary
- References

What is Offset?



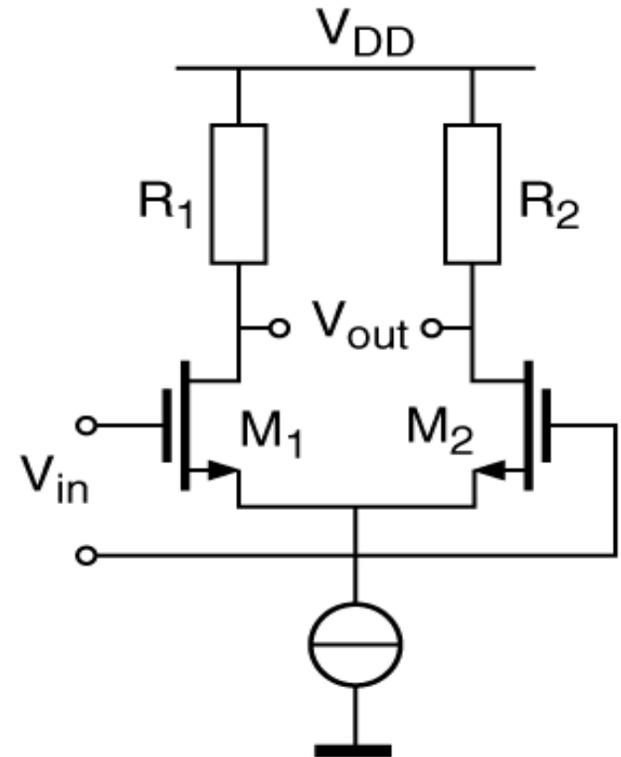
- When the input of a REAL amplifier is shorted, $V_{out} \neq 0$!
- The **offset** V_{os} is the input voltage required to make $V_{out} = 0$. It is typically in the range: $100\mu\text{V}$ to 10mV .
- Note: In CMOS, input offset currents are negligible.

Differential Amplifiers

Differential amplifiers are often used to amplify DC signals.

Their balanced structure is

- Nominally offset free
- Rejects common-mode and power supply interference
- Easily realized in both CMOS and bipolar technologies



Offset in Differential Amplifiers

Component mismatch

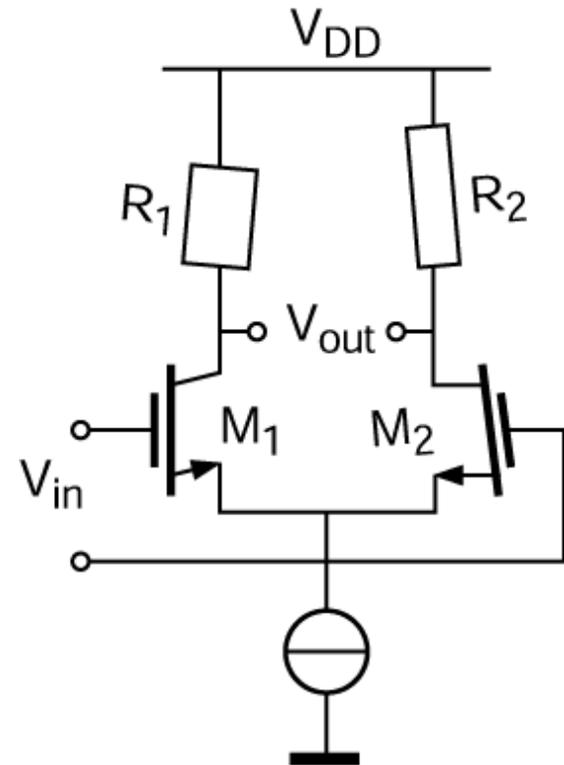
e.g. $R_1 \neq R_2$, $M_1 \neq M_2 \Rightarrow$ **offset**

Mismatch is mainly due to

- Doping variations
- Lithographic errors
- Packaging & local stress

All things being equal

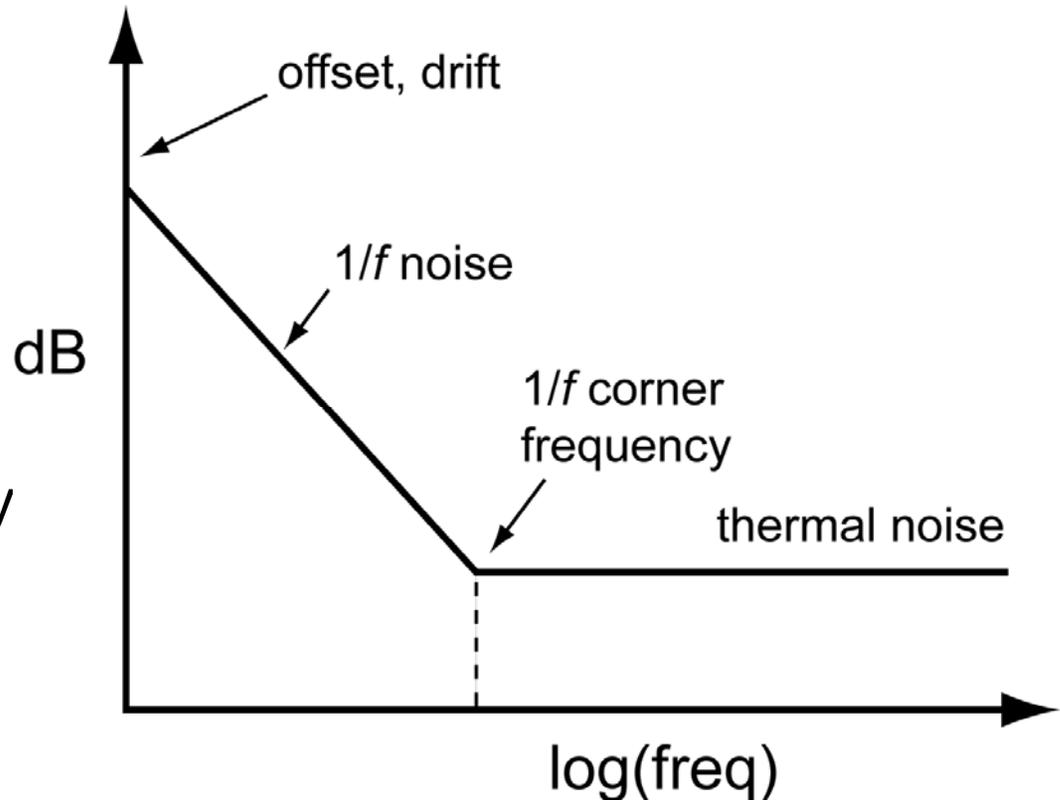
- Bipolar $\Rightarrow V_{os} \sim 0.1\text{mV}$
- CMOS $\Rightarrow V_{os}$ is 10 -100x worse!



Amplifier Behaviour Near DC

Characterized by

- Offset
- Drift
- $1/f$ (flicker) noise
- Thermal noise
- $1/f$ corner frequency



What to Do?

Offset and $1/f$ noise are part of life!

But we can reduce offset “enough” by

1. Using “large” devices and good layout¹ \Rightarrow 1mV
2. Trimming \Rightarrow 100 μ V drift over temperature (MOS)
3. Dynamic offset-cancellation (DOC) techniques \Rightarrow 1 μ V

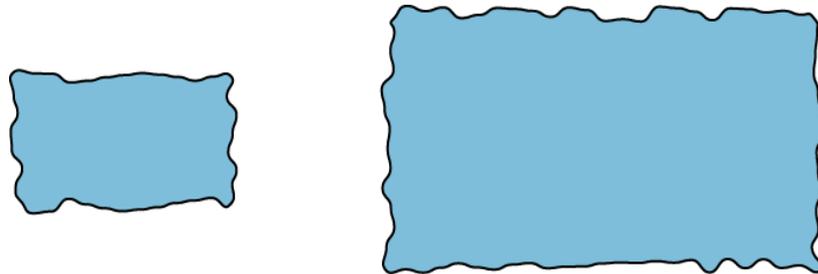
DOC techniques also

- Reduce drift and $1/f$ noise
- Improve PSRR and CMRR

Mismatch

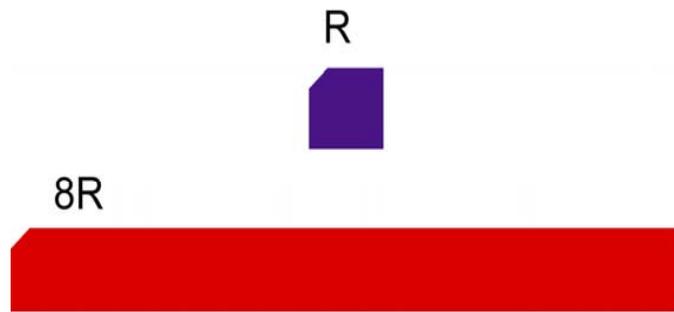
Determined by:

1. Lithographic accuracy e.g. $R = \rho L/W$
 $\Rightarrow \Delta R/R \sim \Delta L/L + \Delta W/W$
 \Rightarrow Matching improves with area!



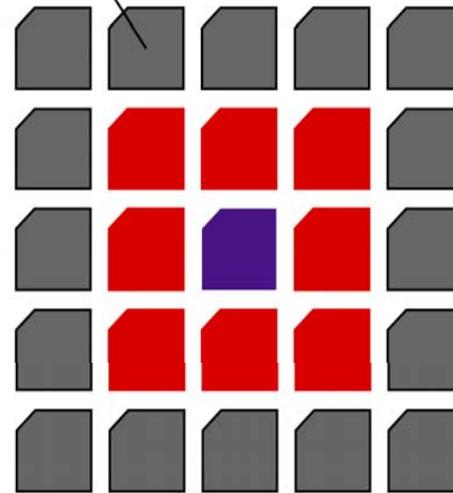
2. Doping Variations $\Rightarrow \Delta R/R$ limited to 0.1% even for large neighboring resistors
3. Mechanical stress due to metal lines or packaging

Good Layout Helps!



Bad Layout

Dummy elements



Good Layout

Good layout \Rightarrow

- Large Devices
- Exclusive use of unit cells (and dummies)
- Currents in unit cells flow in the same direction

Trimming

⇒ Cancel offset by adjusting an on-chip component

- ✓ Low circuit complexity
- ✓ Minimal effect on circuit bandwidth

- ✗ Requires test equipment
- ✗ Does not reduce drift or $1/f$ noise
- ✗ Requires an analog memory, e.g.
 - Fusible links (Zener diodes)
 - Laser-trimmed resistors
 - PROM + DAC (component array)

Trimming a BJT Differential Amp

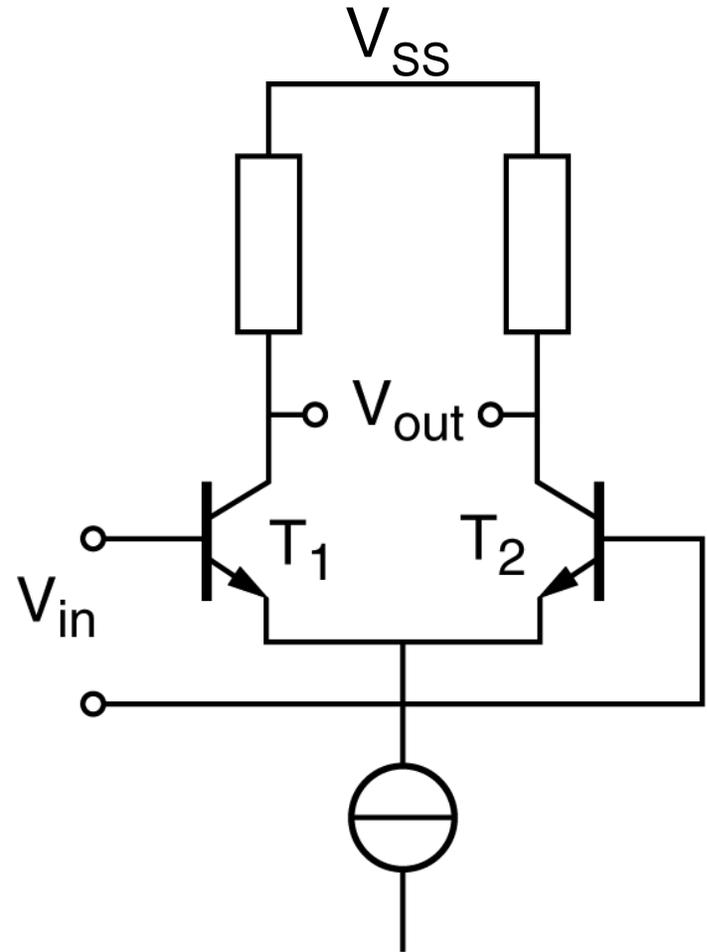
$$V_{os} = V_T \left(\frac{\Delta R}{R} + \frac{\Delta I_S}{I_S} \right)$$

$$V_T = kT/q = 26\text{mV} @ 300\text{K}$$

- $V_{OS} \sim 0.1\text{mV}$ is possible!

After trimming (via ΔR)

- $V_{OS} \sim 0$
- Also temperature coefficient of V_{OS} ($\text{TC}V_{os}$) ~ 0



Trimming a MOSFET Diff. Amp (1)

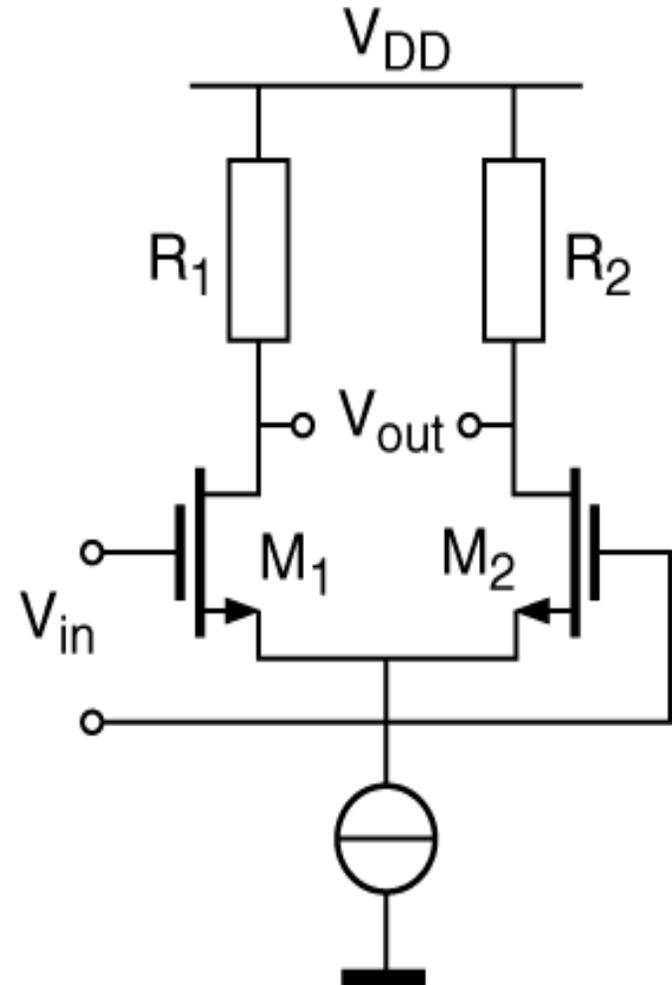
$$V_{os} = \Delta V_{TH} + \frac{I_D}{g_m} \left(\frac{\Delta R}{R} + \frac{\Delta \beta}{\beta} \right)$$

where $\beta = \mu C_{ox}(W/L)$

- $\Delta V_{TH} \sim 1\text{mV}$
and temp. independent
- I_D/g_m is temp. dependent

After trimming

- $V_{OS} \sim 0$ but $TCV_{OS} \sim 1\mu\text{V}/^\circ\text{C}$
- Much worse than bipolar!



Trimming a MOSFET Diff. Amp (2)

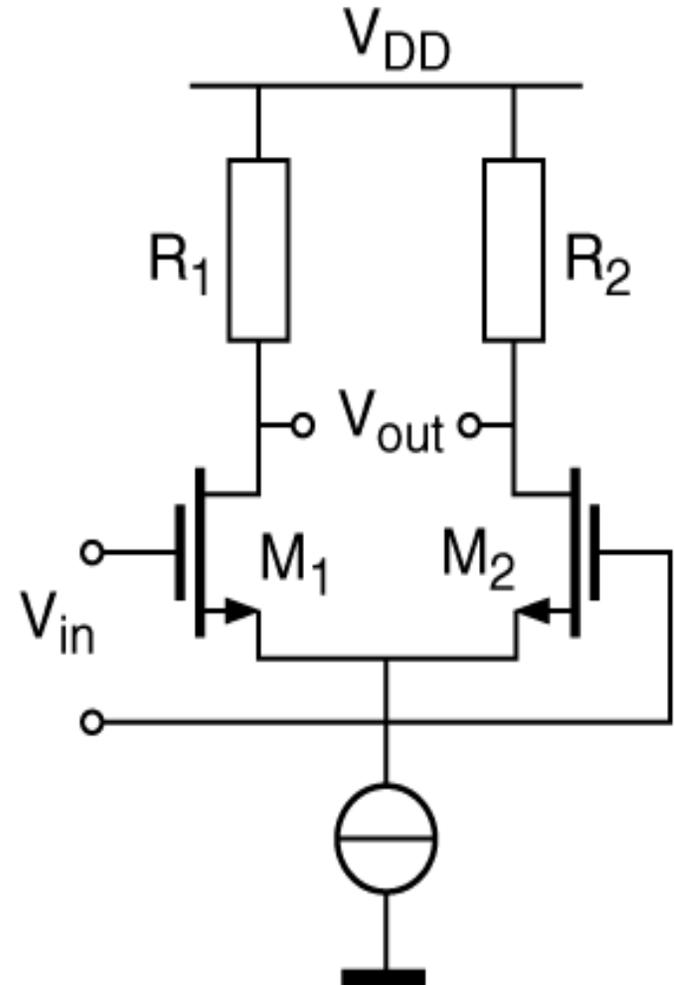
$$V_{os} = \Delta V_{TH} + \frac{I_D}{g_m} \left(\frac{\Delta R}{R} + \frac{\Delta \beta}{\beta} \right)$$

where $\beta = \mu C_{ox}(W/L)$

Better trimming

- Trim V_{TH} & β *independently* at room temperature!
 $\Rightarrow TCV_{OS} \sim 0.33\mu V/^{\circ}C$ (3σ)

M. Bolatkale et al., ISSCC 08



Trimming: Summary

- Simple, does not limit BW
- Does not reduce drift or $1/f$ noise
- Requires test equipment and an analog memory

- Works very well with BJT diff. amps since it nulls both V_{OS} and TCV_{OS}
- Works less well with MOSFET diff. pairs poorly defined $TCV_{OS} \Rightarrow 100\mu V$ drift over temp.

- Higher performance \Rightarrow Dynamic offset cancellation

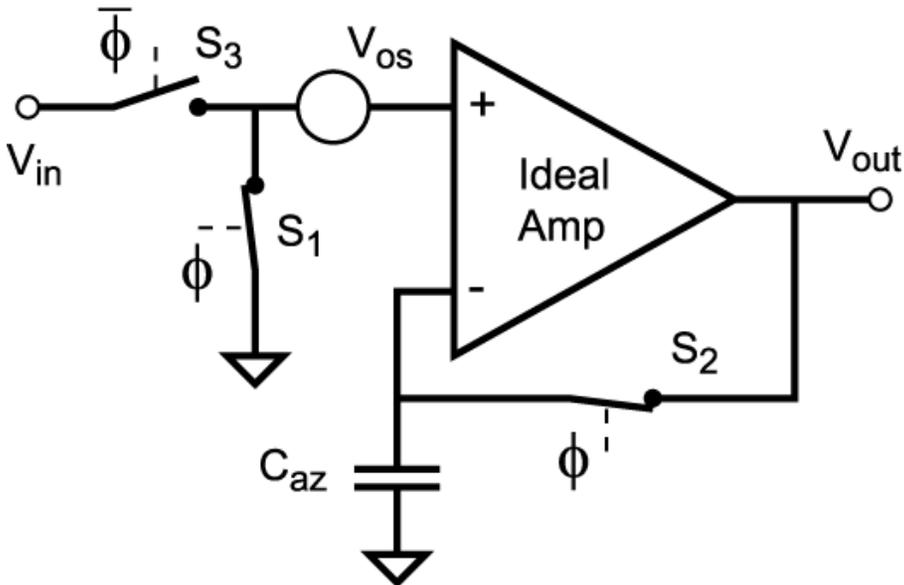
Dynamic Offset Cancellation (DOC)

Two basic methods²

1. Measure the offset somehow and then subtract it from the input signal \Rightarrow Auto-zeroing
2. Modulate the offset away from DC and then filter it out \Rightarrow Chopping

Both methods also reduce low frequency noise and improve common-mode & power supply rejection

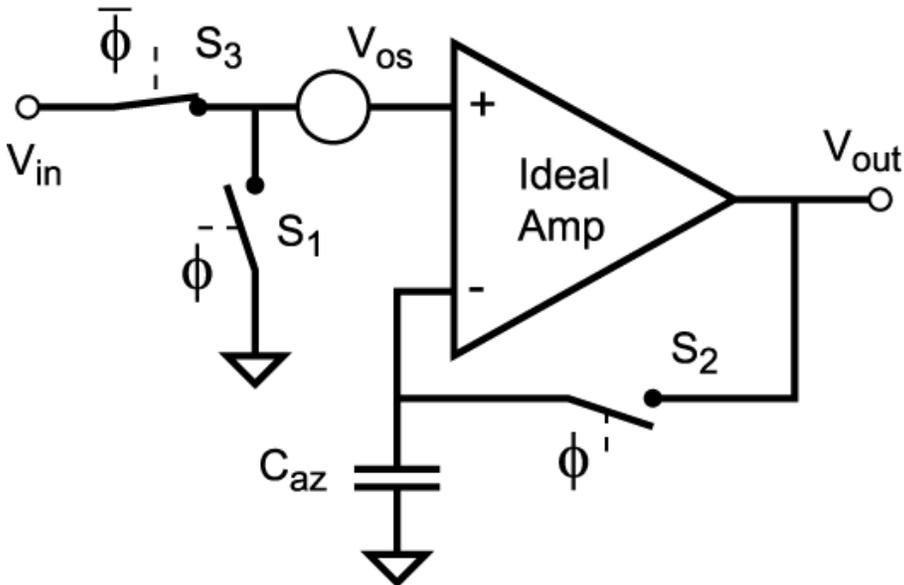
Auto-zero Principle (1)



Auto-zero phase

- S_1, S_2 closed, S_3 open $\Rightarrow V_{out} = V_{os}$
 \Rightarrow offset stored on C_{az}
- Amplifier is unavailable

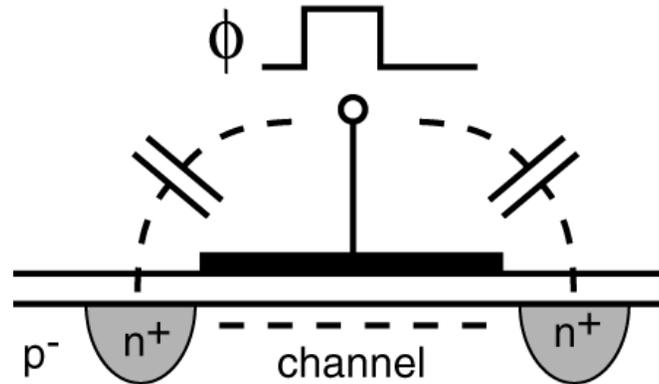
Auto-zero Principle (2)



Amplification phase:

- S_1, S_2 open, S_3 closed $\Rightarrow V_{in}$ is amplified
- *Finite* voltage gain $A \Rightarrow$ error in sampled offset \Rightarrow input-referred residual offset $V_{res} = V_{os}/(A+1)$
- Charge injection is also a problem ...

Charge Injection (1)

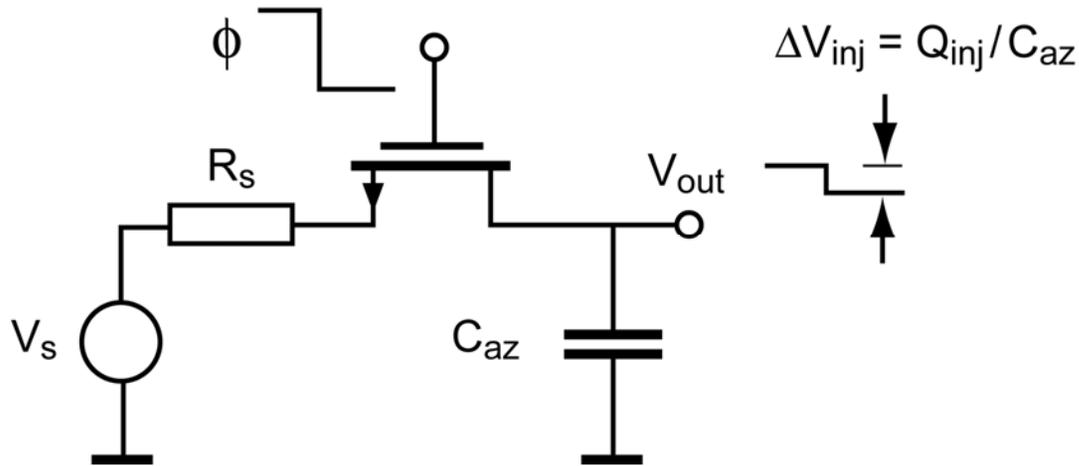


Consists of two components

1. Channel charge, $Q_{ch} = WLC_{ox}(V_{GS} - V_t)$
2. Charge transfer via the overlap capacitance between gate and source/drain \Rightarrow clock feed-through

Problematic when a MOSFET switches **OFF**.

Charge Injection (2)

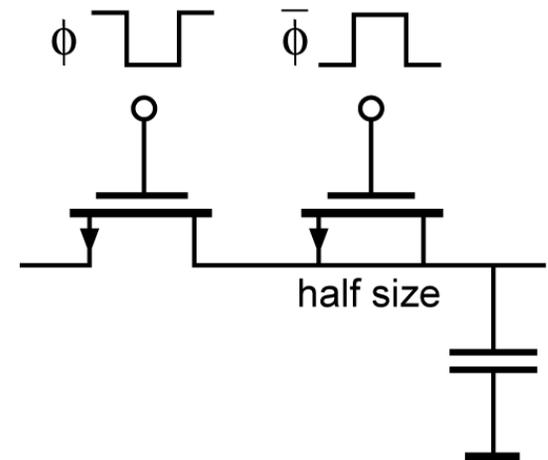
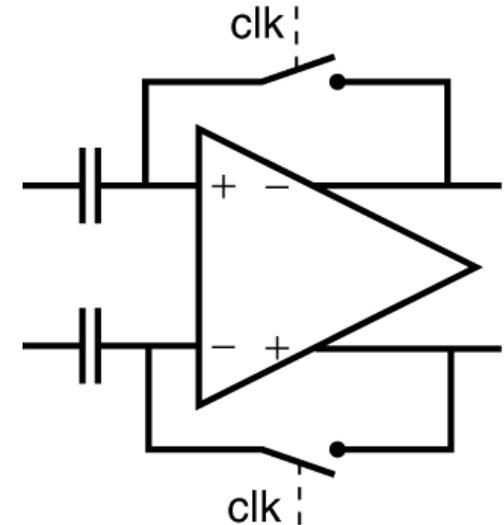


CI error voltage ΔV_{inj} depends on many factors^{3,4}

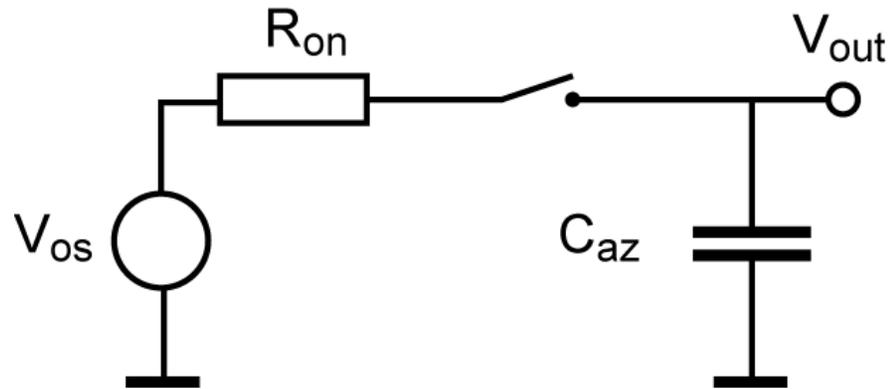
- Source voltage and impedance
- Clock amplitude & slew rate
- Transistor area (WL) (smaller \Rightarrow better)
- Value of C_{az} (larger \Rightarrow better)
- In $0.7\mu\text{m}$ CMOS, minimum-size NMOS, 2.5V step & $10\text{pF} \Rightarrow \Delta V_{inj} \sim 250\mu\text{V}$

Mitigating Charge Injection (CI)

- Use differential topologies
 - ⇒ CI is a common-mode signal
 - ⇒ 1st order cancellation
- Use small switches & big caps (subject to noise & BW requirements)
- For single-ended topologies dummy switches help^{3,4}
- **But** area of main switch will be ~2x minimum size ⇒ more CI ⇒ limited benefit

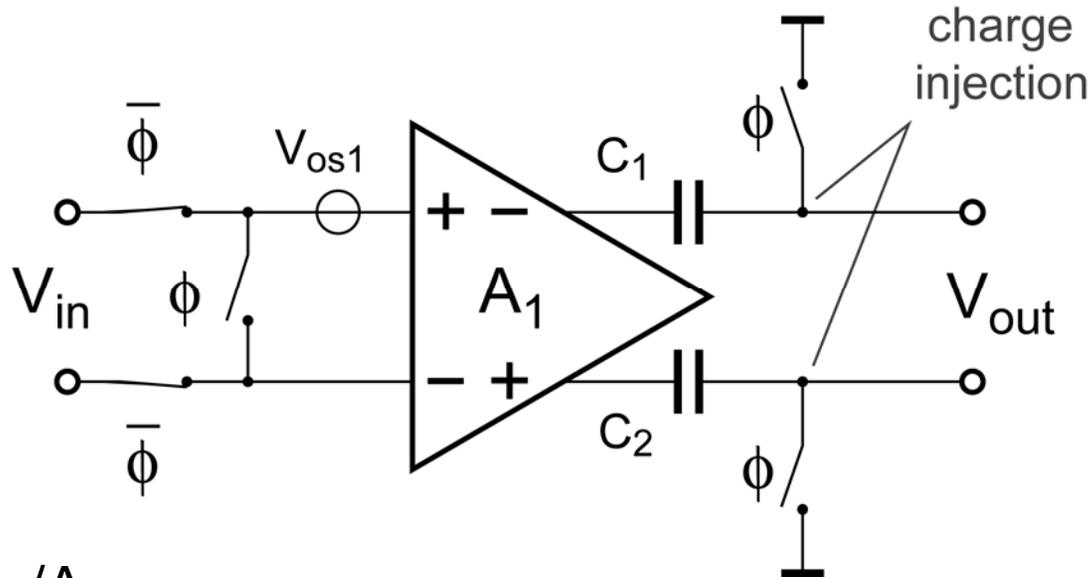


Sampling the offset: kT/C noise



- Thermal noise of R_{on} is filtered by C_{az}
- When the switch is opened the instantaneous noise voltage is held on C_{az}
- Total noise power = kT/C_{az} (10pF @ 300K \Rightarrow 20.3 μ V)
- Large capacitance \Rightarrow accurate sampling of V_{os}

Output-Referred Auto-zeroing



$$V_{res} = \Delta V_{inj}/A_1$$

- Amplifier's offset is now completely cancelled^{5,6}
- Gain of 1st amplifier reduces effects of charge injection and kT/C noise \Rightarrow sampling capacitors can be smaller
- **But** too much gain \Rightarrow clipping! $\Rightarrow A_1$ is typically < 200

Residual Offset of Auto-zeroing

Determined by

- Charge injection
- Leakage on C_{az}
- Finite amplifier gain

In practice

- Minimum size switches
- C_{az} as large as possible (sometimes external)
- Multi-stage amplifier topologies

Results in residual offsets of 1-10 μ V

Residual Noise of Auto-zeroing (1)

$$V_{n,az}(f) = V_n(f) * (1 - H(f))$$

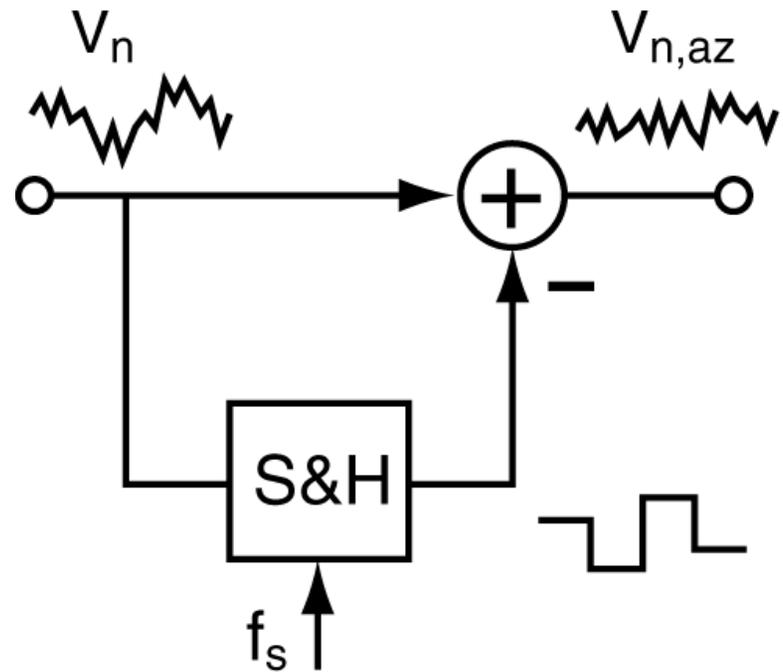
$H(f)$ is the frequency response of the S&H

$$H(f) = \text{sinc}(\pi f / f_s) \Rightarrow \text{LPF}$$

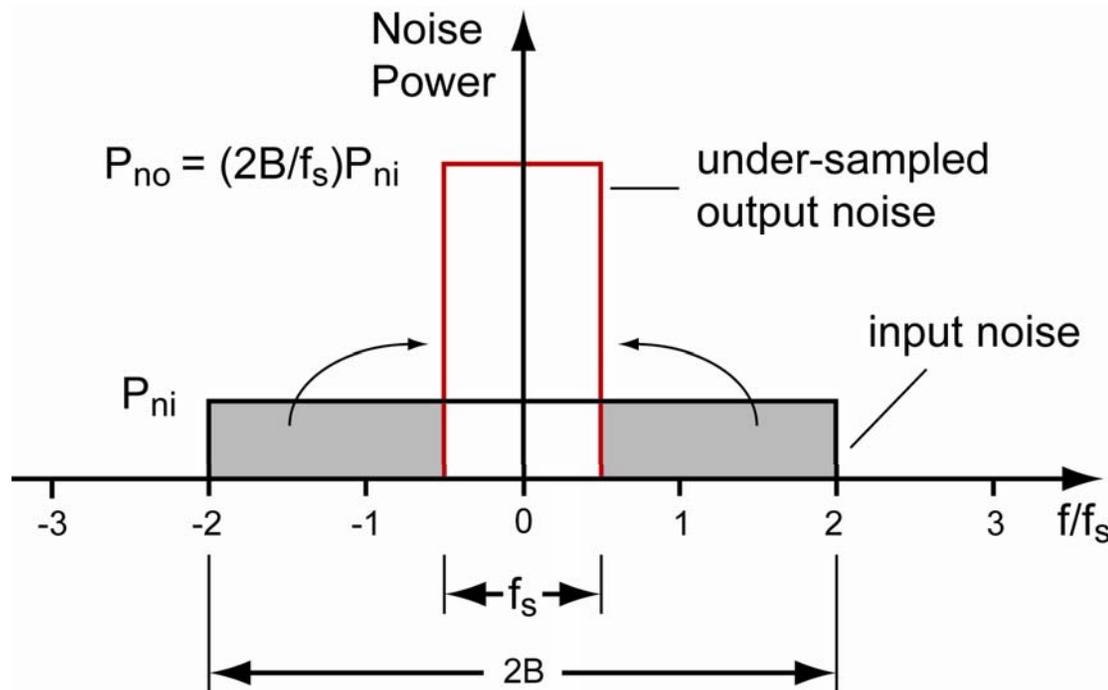
$\Rightarrow 1 - H(f)$ is a HPF

\Rightarrow reduction of both offset and $1/f$ noise

\Rightarrow but sampled thermal noise will fold back to DC

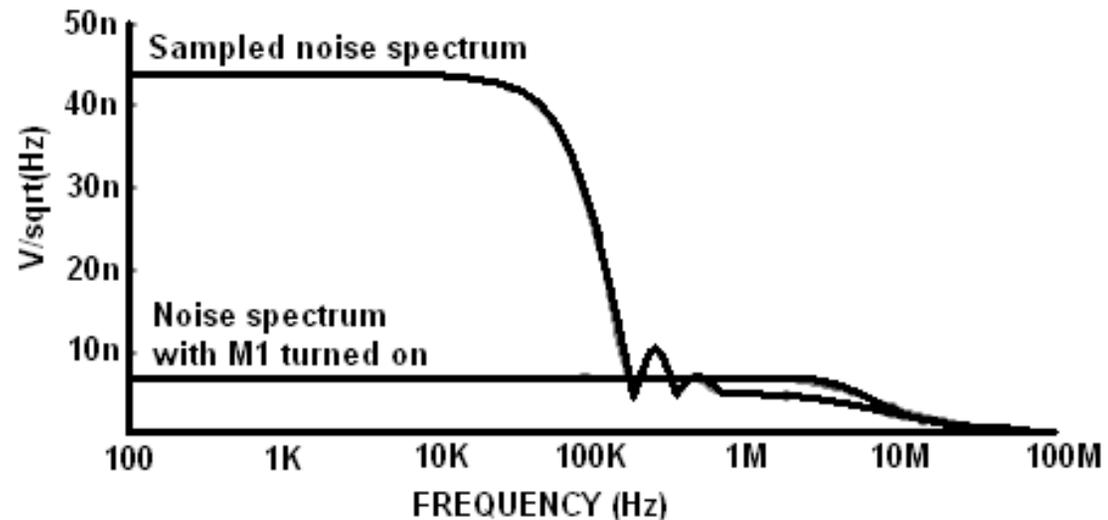
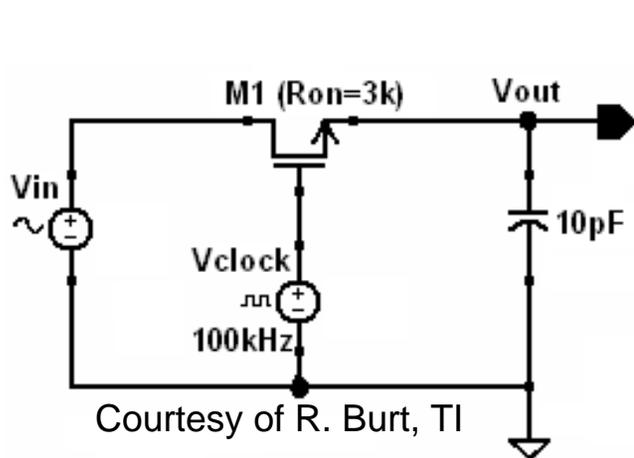


Residual Noise of Auto-zeroing (2)



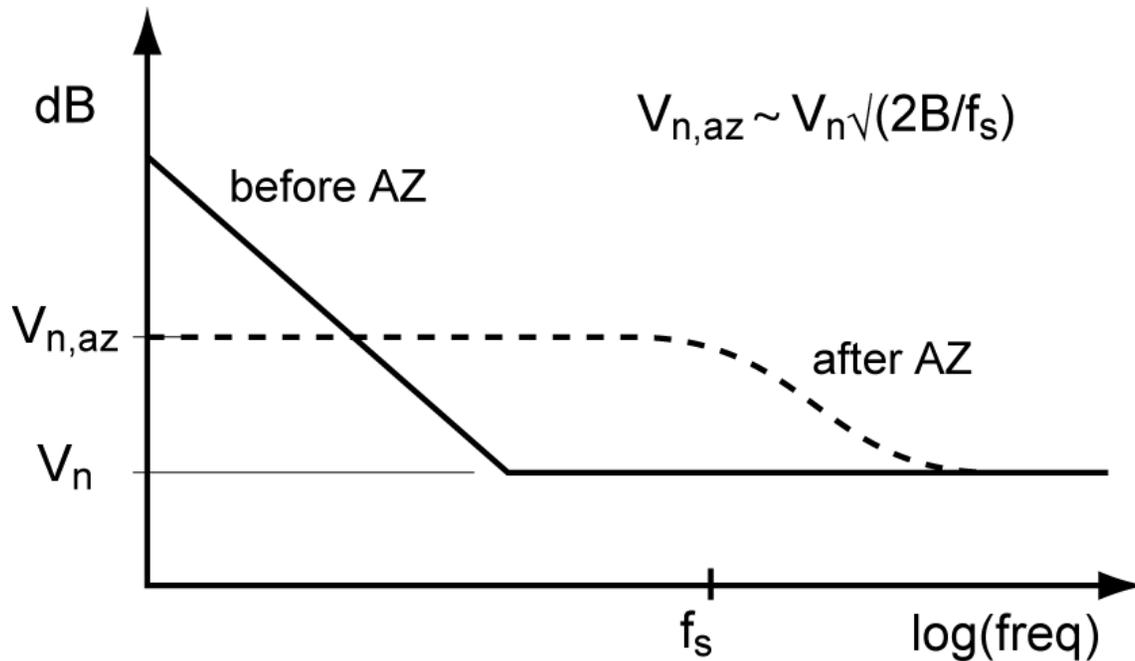
- **Noise** bandwidth $B > f_s$ (due to settling considerations) \Rightarrow input noise will fold back (alias) to DC
- The result is then LP filtered by the $\text{sinc}(\pi f/f_s)$ function

Residual Noise of Auto-zeroing (3)



- S&H with 100kHz clock & 50% duty-cycle
- Noise aliasing \Rightarrow 6x increase in LF noise voltage!
- Notches at multiples of $2f_{\text{clock}}$ due to 50% duty cycle²
- Sampled noise spectrum obtained with $P_{\text{noise}}^{9,10}$

Residual Noise of Auto-zeroing (4)



- Detailed analysis² \Rightarrow significant reduction of $1/f$ noise **IF** $f_s \gg 1/f$ corner frequency
- Noise aliasing \Rightarrow LF power increased by the under-sampling factor (USF) = $2B/f_s \Rightarrow$ factor 3 to 6 in volts

Continuous Output

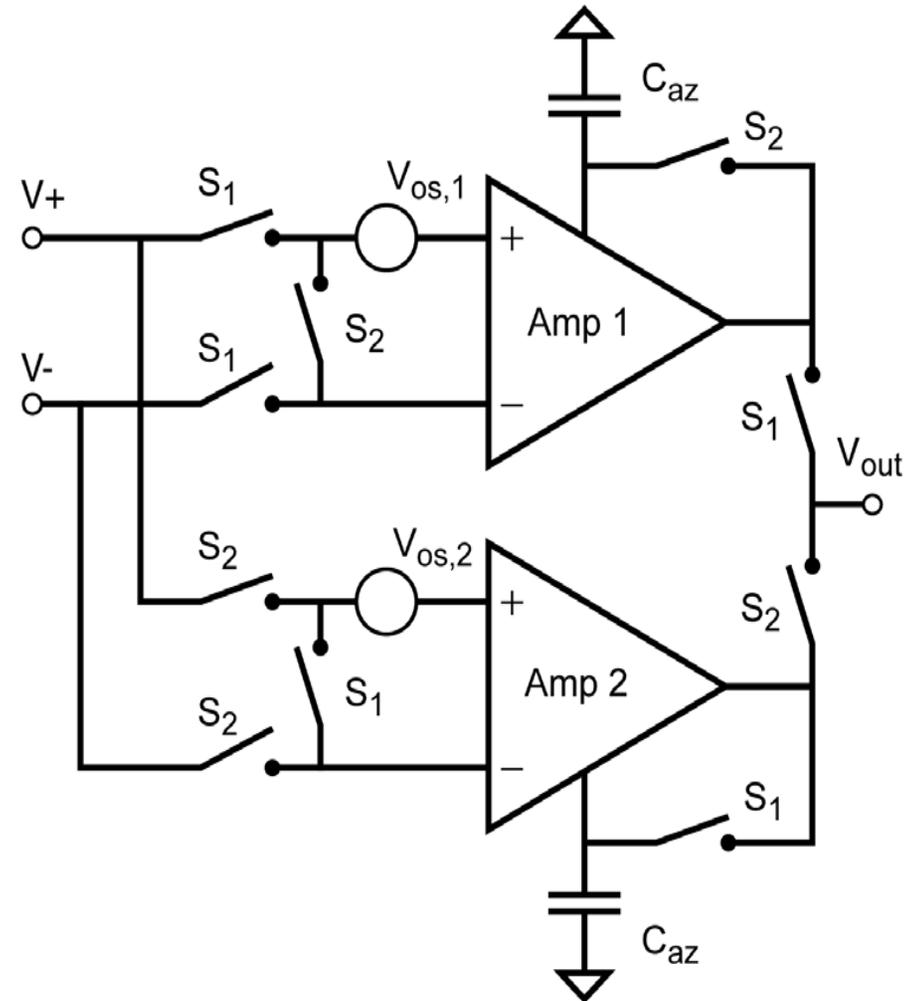
- Basic auto-zero principle \Rightarrow the amplifier is not continuously available

Solutions

- Two AZ'ed amplifiers connected in parallel
 \Rightarrow Ping-pong architecture
- An AZ'ed amplifier nulls the offset of another amplifier
 \Rightarrow Offset stabilization

AZ Ping-Pong Amplifier

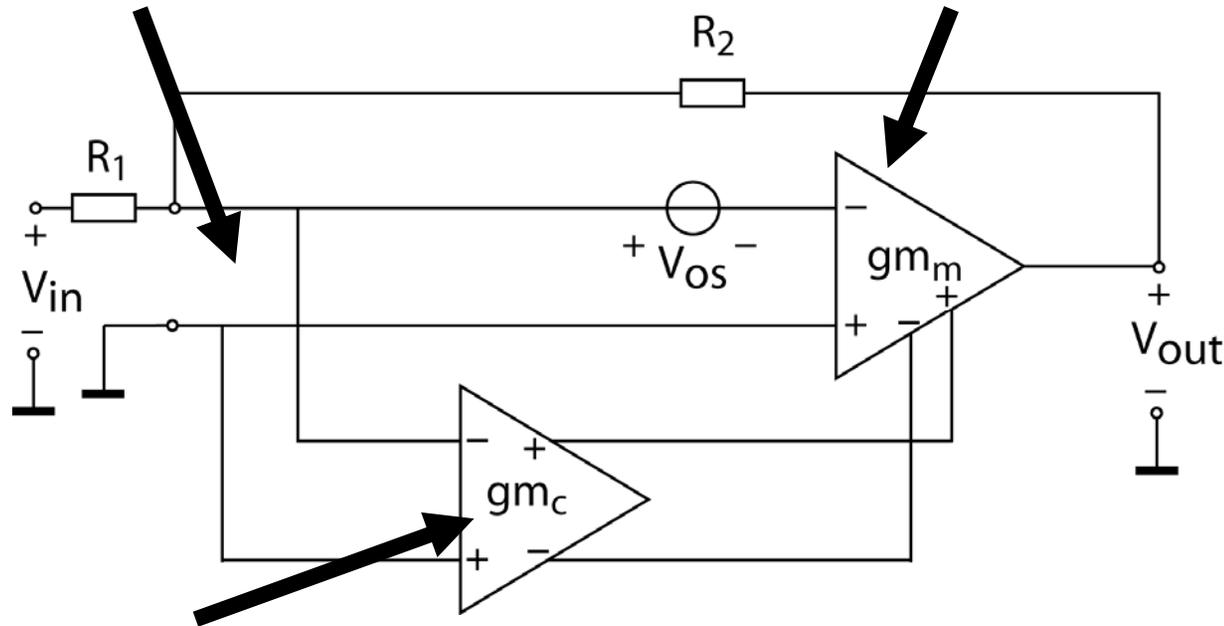
- Input signal “bounced” between two auto-zeroed amplifiers^{11,12}
- Output V_{out} is then a quasi-continuous signal
- But switching spikes limit performance
- Randomized switching reduces spikes¹³



Offset Stabilization (OS)

Negative feedback
⇒ offset visible at input

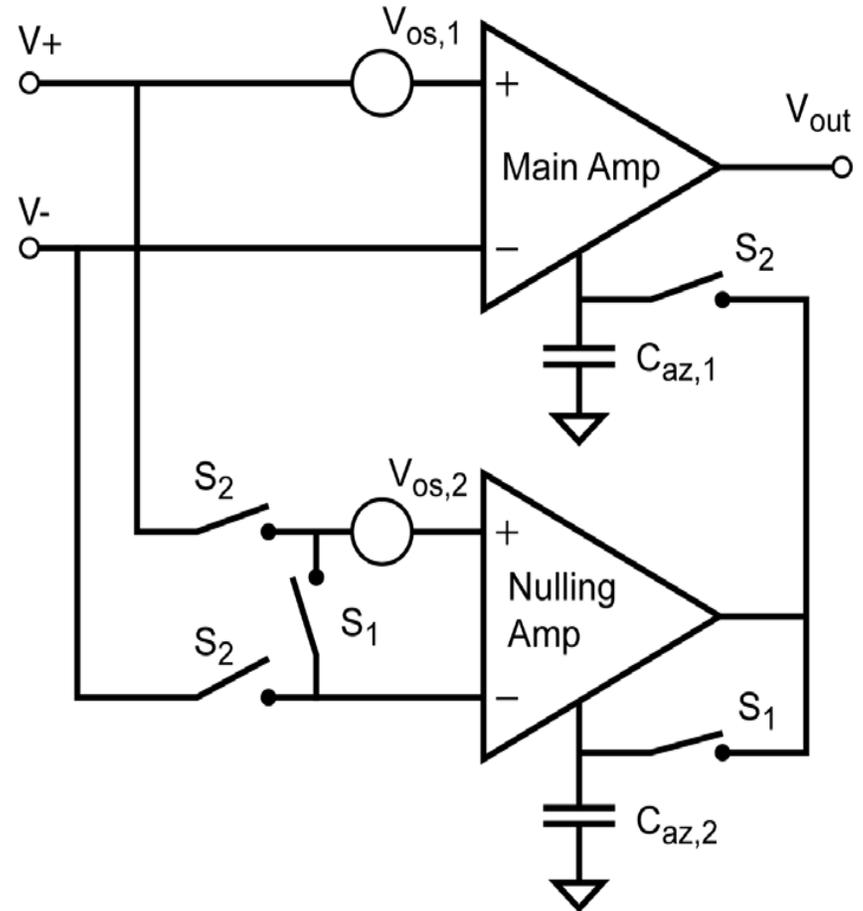
High bandwidth
main amplifier



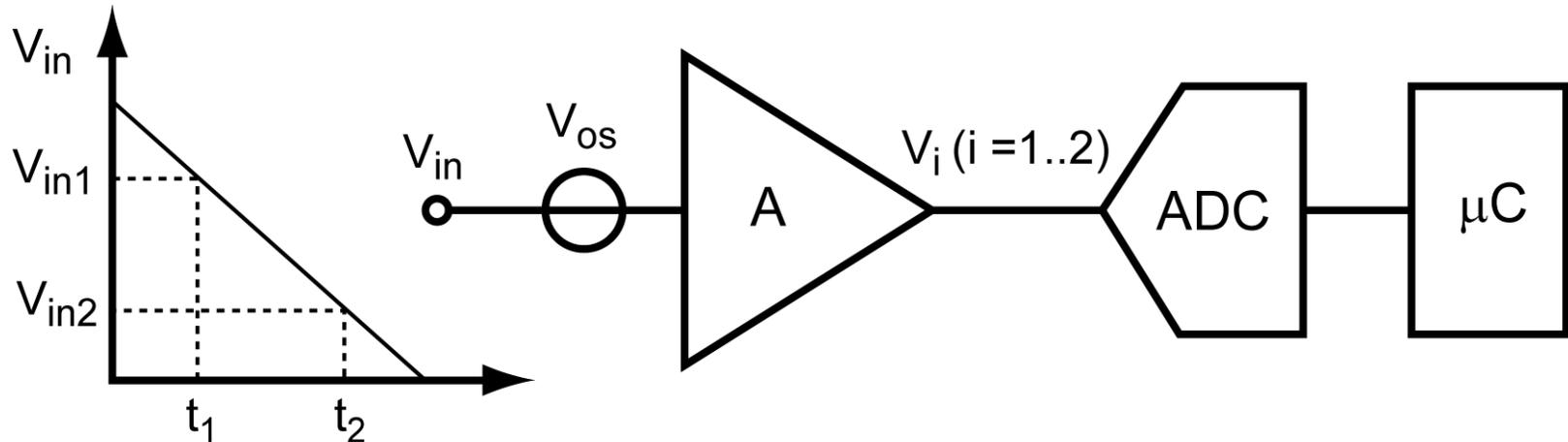
- Also called continuous-time AZ
- Low bandwidth, low offset compensating amplifier
⇒ Auto-zeroed or chopped

AZ Offset-Stabilized Amplifier

- Auto-zeroed nulling amp cancels the offset of main amplifier^{14,15}
- Continuous output and less spikes
- But poor overload performance, i.e. when $V_+ - V_- > V_{os}$
- Amplifier cannot be used as a comparator



Correlated Double Sampling (CDS)

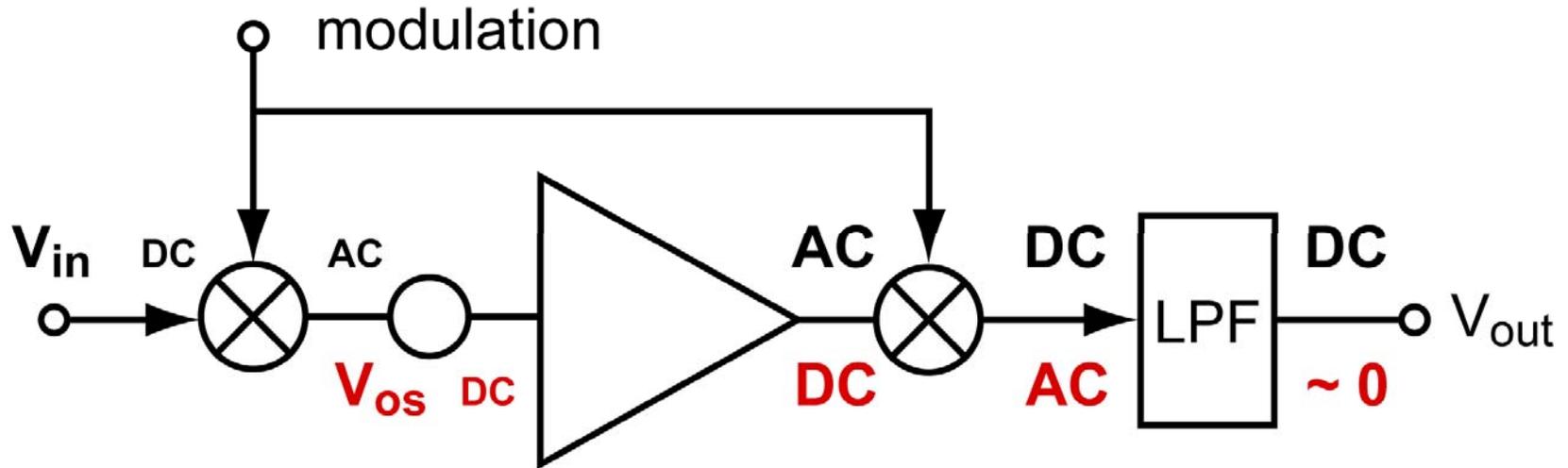


- Sometimes only a signal **difference** is required e.g. in image sensors
- Phase 1: $V_1 = A(V_{in1} + V_{os})$
- Phase 2: $V_2 = A(V_{in2} + V_{os})$
- $\Rightarrow (V_1 - V_2) = A(V_{in1} - V_{in2})$
- CDS also suppresses $1/f$ noise

Auto-Zeroing: Summary

- Offsets in the range of 1-10 μ V can be achieved
- No loss of bandwidth with appropriate amplifier topologies (ping-pong, offset-stabilization)
- Sampled data technique \Rightarrow kT/C noise is an issue
- Noise aliasing will occur \Rightarrow increased LF noise
- DOC technique of choice in sampled-data systems e.g. switched-capacitor filters, ADCs etc.

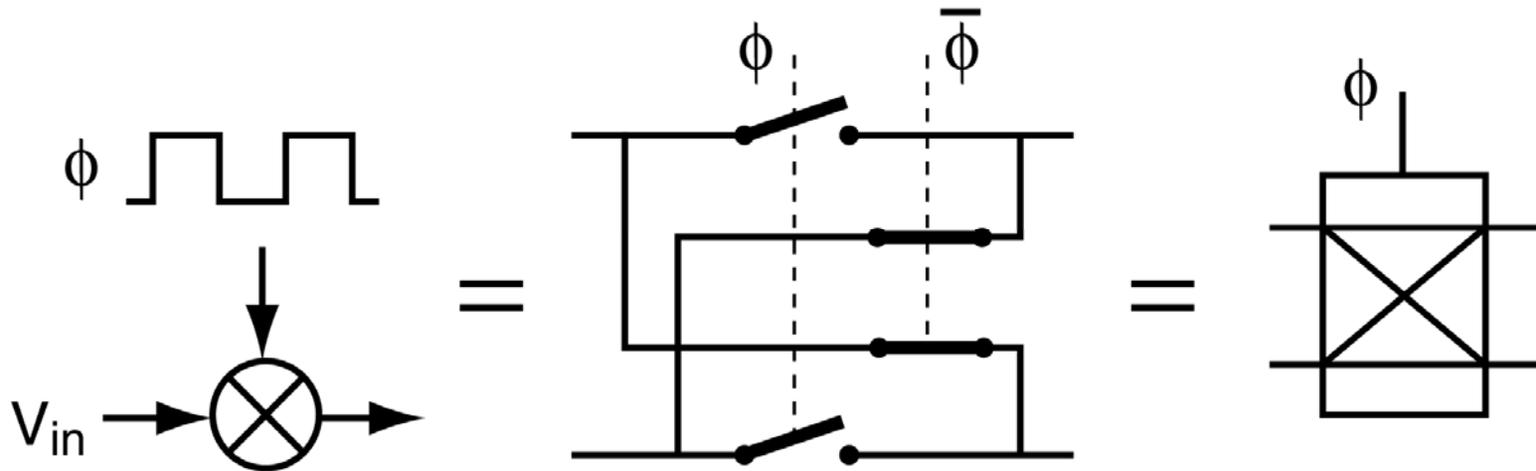
Chopping Principle



Signal is modulated, amplified and then demodulated¹⁶

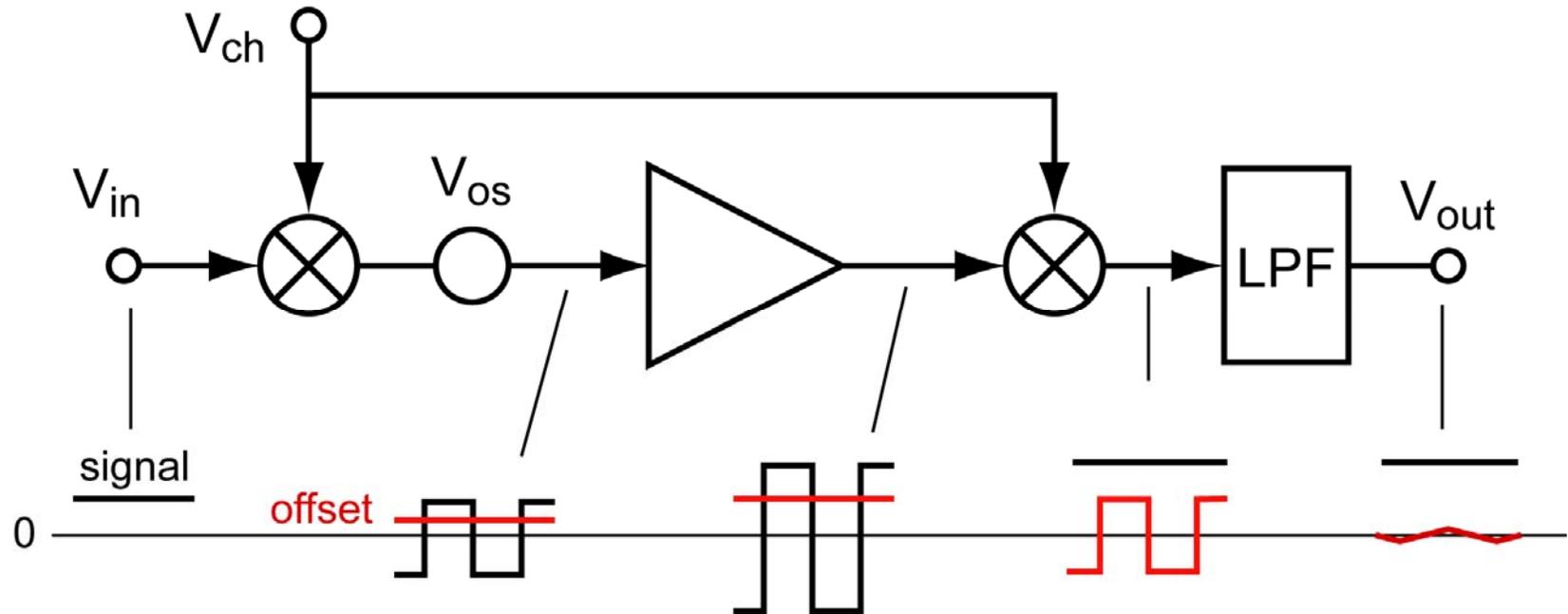
- + Output signal is continuously available
- Low-pass filter required

Square-wave Modulation



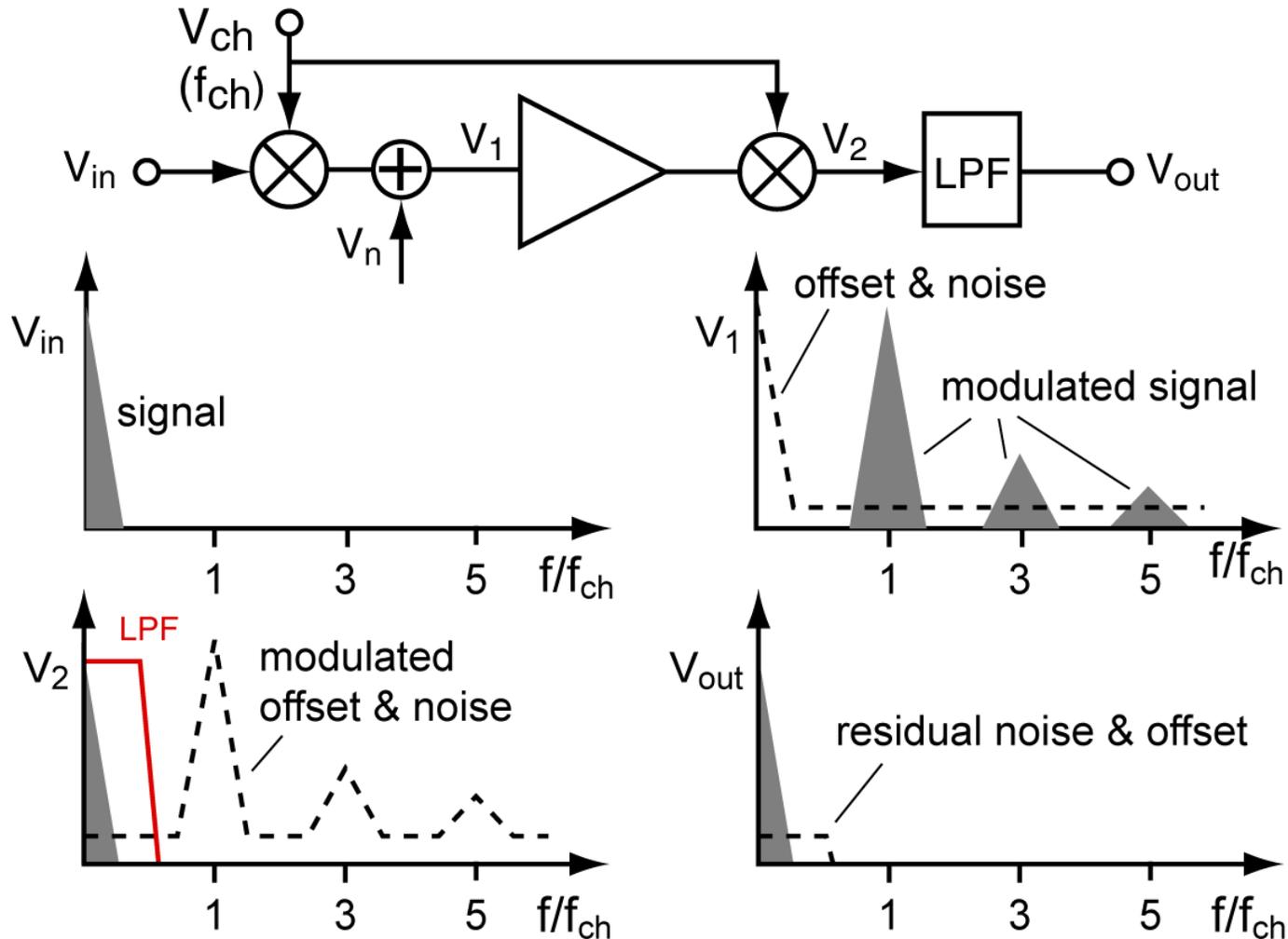
- Easily generated modulating signal
- Modulator is a simple polarity-reversing switch
- Switches are easily realized in CMOS

Chopping in the Time Domain

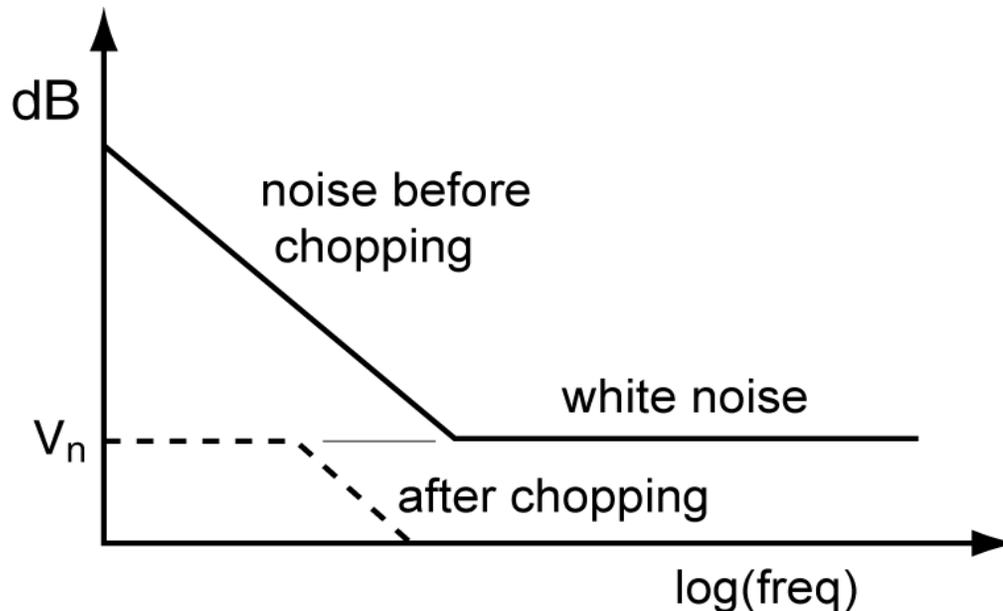


- $V_{res} = 0$ **IF** duty-cycle of V_{ch} is exactly 50% \Rightarrow flip-flop
- If $V_{os} = 10\text{mV}$ & $f_{ch} = 50\text{kHz}$, then 1ns skew $\Rightarrow V_{res} = 1\mu\text{V}$

Chopping in the Frequency Domain

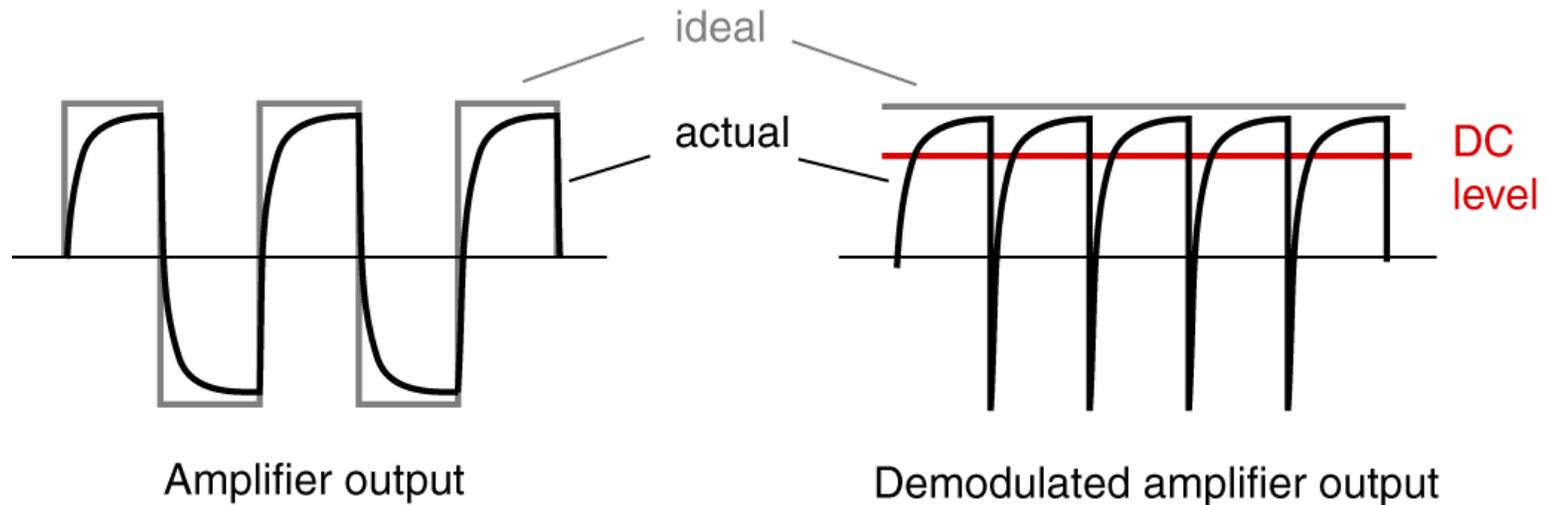


Residual Noise of Chopping



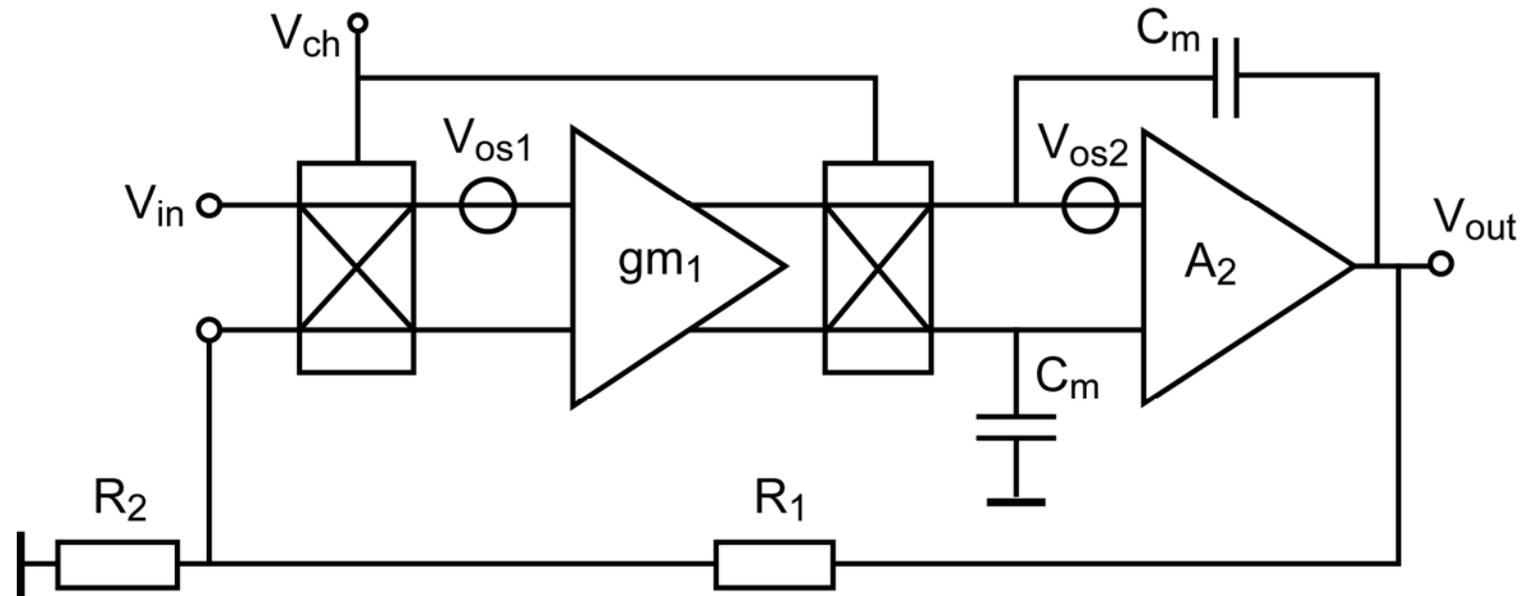
- $1/f$ noise is **completely** removed
IF $f_{ch} > 1/f$ corner frequency
- Significantly better than auto-zeroing!

Bandwidth & Gain Accuracy



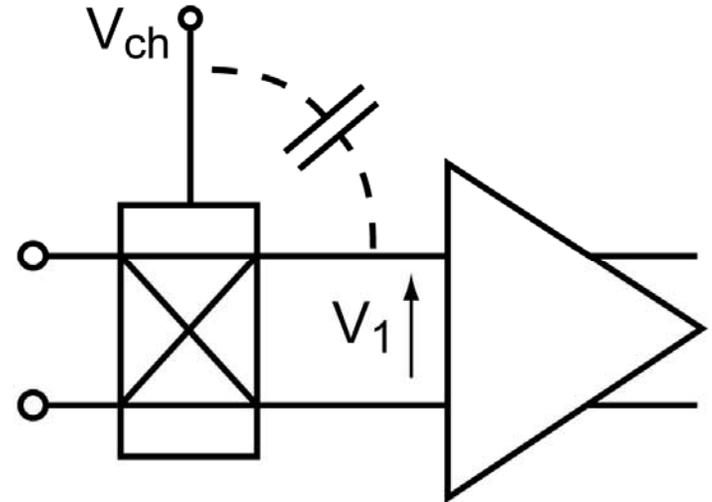
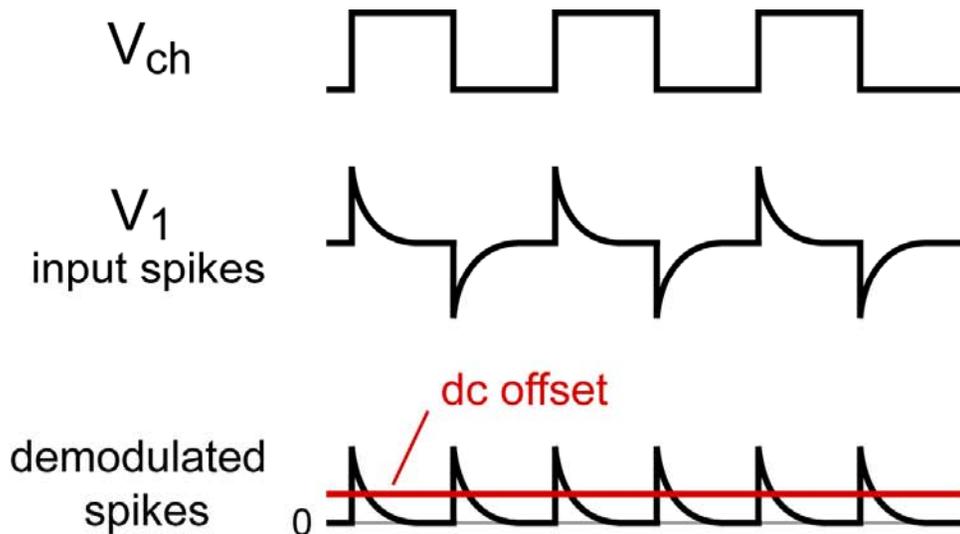
- Limited BW \Rightarrow lower effective gain A_{eff}
and chopping artifacts at even harmonics of f_{ch}
- Gain error $< 10\% \Rightarrow \text{BW} > 6.4f_{\text{ch}}$

Chopper Opamp with Feedback



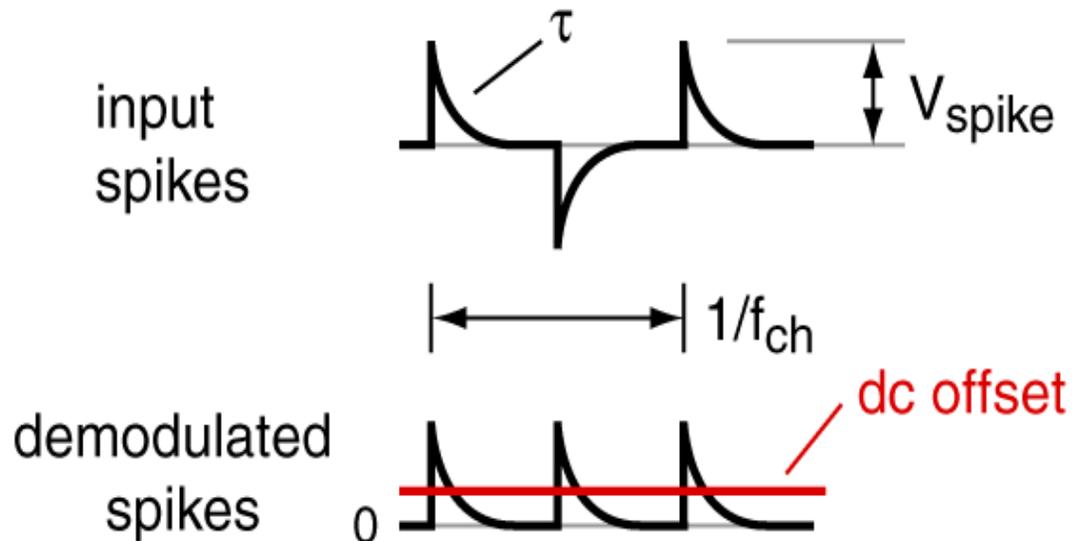
- Feedback resistors \Rightarrow Accurate gain^{17,18}
- To suppress V_{os2} , A_1 should have high gain
- Miller capacitors C_m also suppress ripple
- Minimum ripple \Rightarrow high chopping frequencies

Residual Offset of Chopping (1)



- Due to mismatched charge injection and clock feed-through at the input chopper^{19,20}
- Causes a typical offset of 1-10 μ V
- Input spikes \Rightarrow bias current (typically 50pA)

Residual Offset of Chopping (2)



- Residual offset² = $2f_{\text{ch}} V_{\text{spike}} \tau$
- Spike shape (τ) depends on source impedance e.g. feedback resistors around an opamp

Design Considerations

Input chopper

- Use minimum size switches
- Good layout \Rightarrow symmetric, balanced clock coupling
- Ensure that switches “see” equal impedances
- Use a flip-flop to ensure an exact 50% duty-cycle

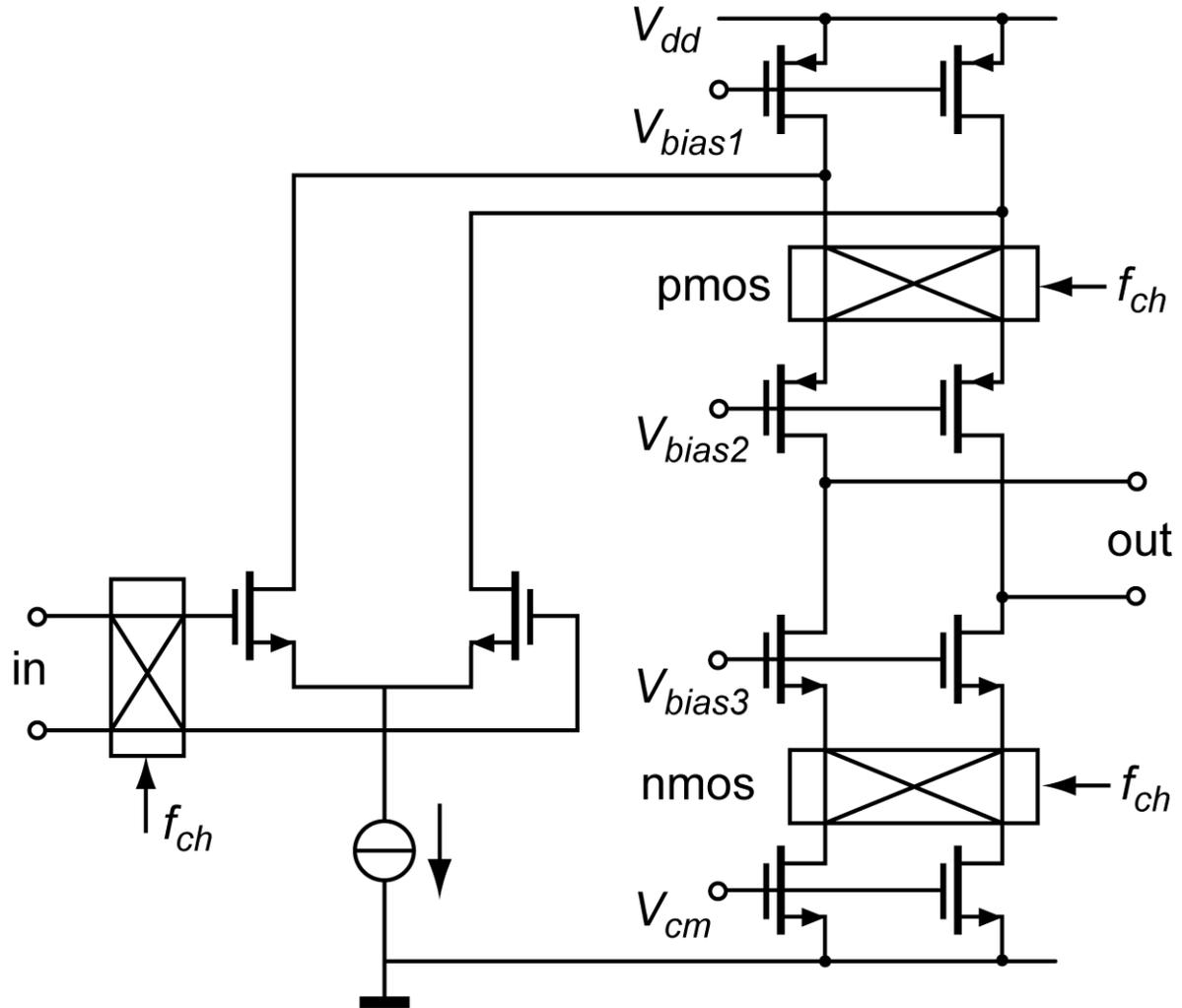
Chopping frequency f_{ch}

- Higher than $1/f$ noise corner frequency
- Not **too** high, as the residual offset increases with f_{ch}

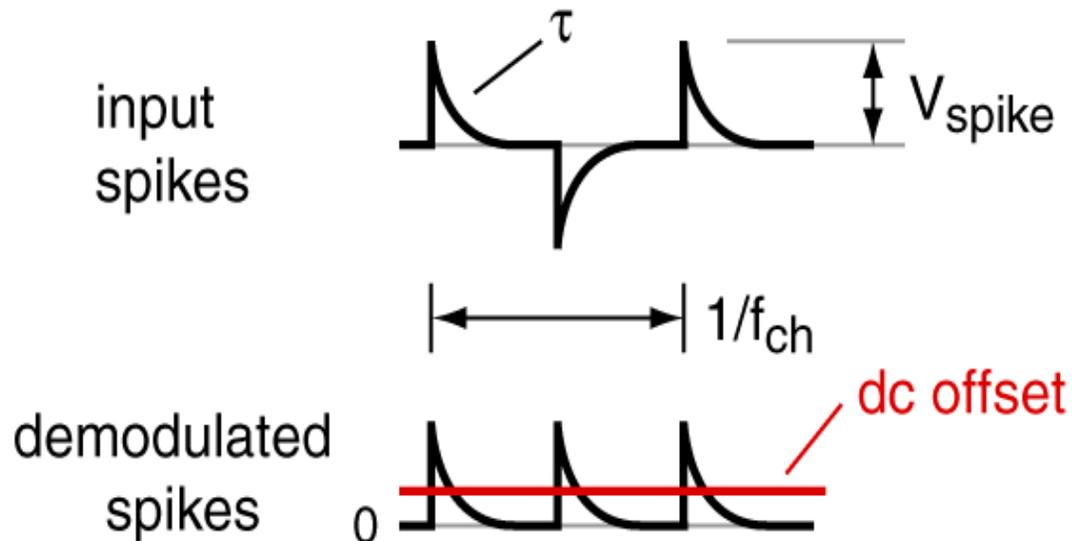
Amplifier BW $\gg f_{ch}$ to minimize gain errors

Chopped Transconductor²²

- Choppers see low & symmetric impedances
- Allows high freq chopping
- PMOS chopper demodulates signal
- NMOS chopper DEMs NMOS current sources

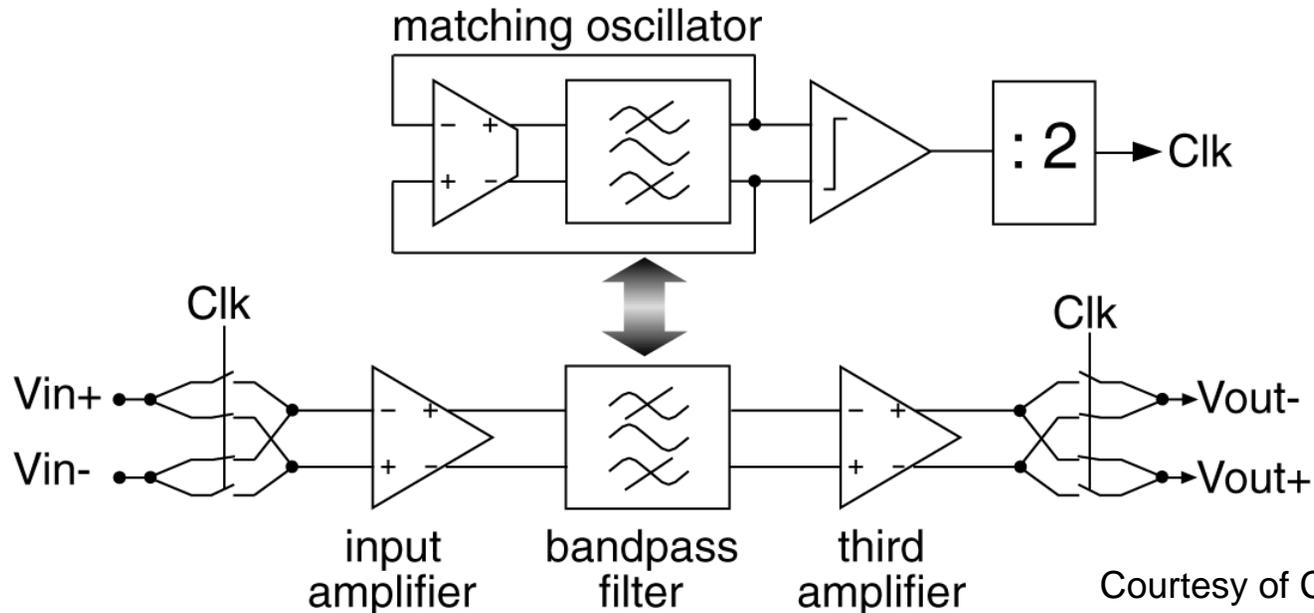


Lower Residual Offset



- Residual offset² = $2f_{\text{ch}} V_{\text{spike}} \tau$
- Low residual offset \Rightarrow reduce chopping frequency, reduce load impedances OR reduce spike amplitude

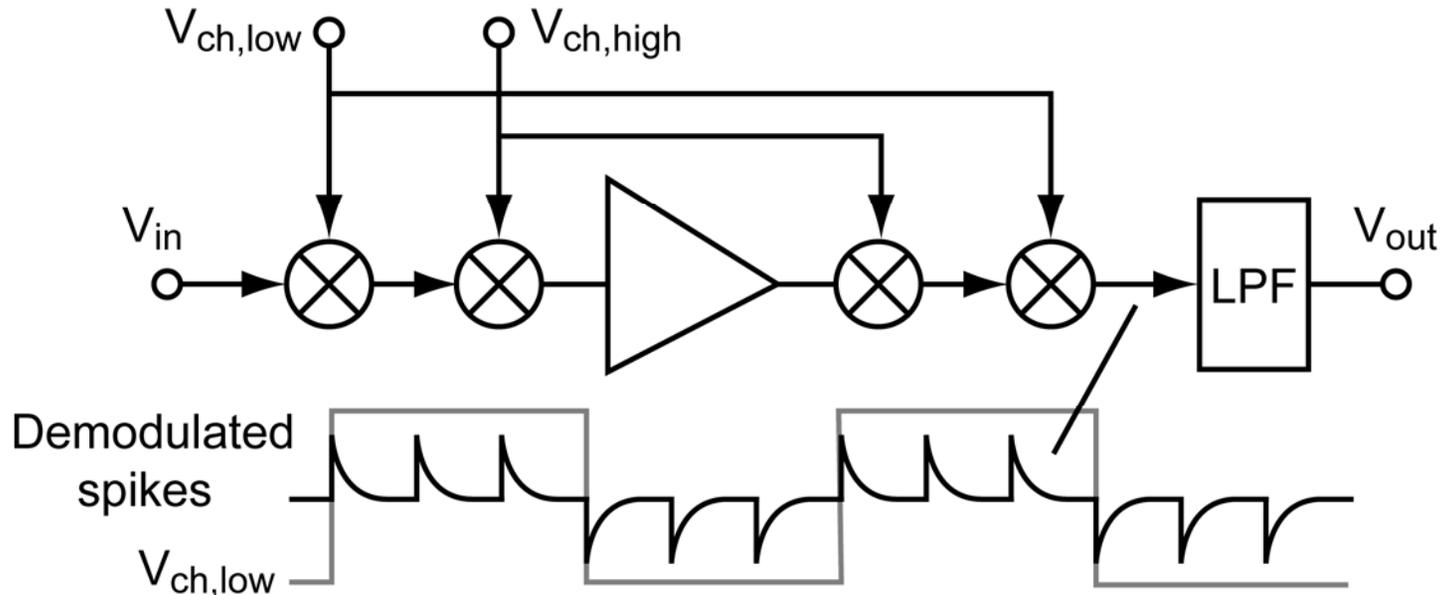
Band-Pass Filtering



Courtesy of C. Hagleitner, IBM

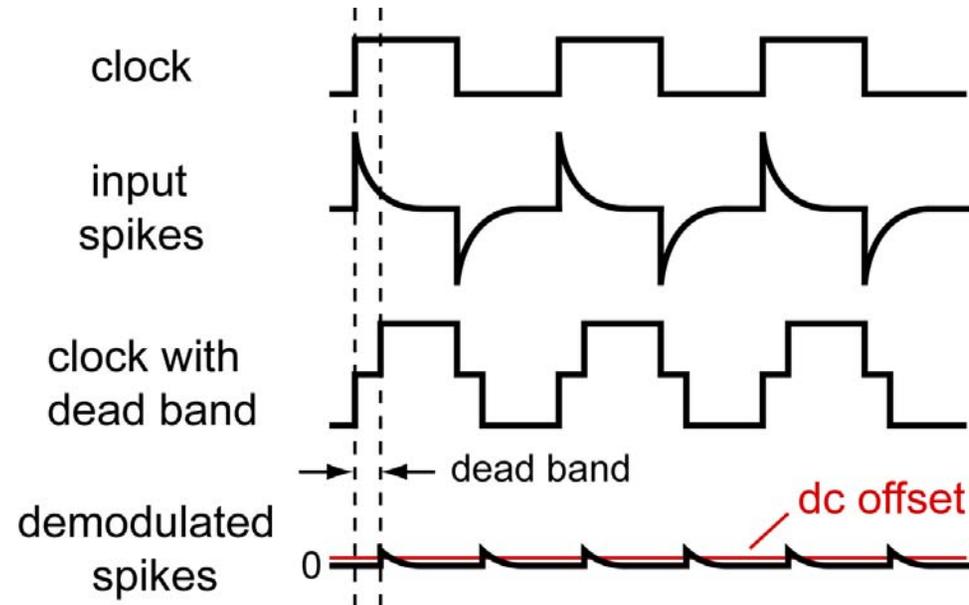
- Spike spectrum is “whiter” than that of modulated signal
⇒ BP filter will reduce **relative** spike amplitude^{19,23,24}
- Clock frequency tracks BP filter's center frequency
⇒ low Q filter, $Q \sim 5$
- Residual offset $\sim 0.5\mu\text{V}$!

Nested Chopping



- Inner HF chopper removes $1/f$ noise
- Outer LF chopper removes residual offset²¹
- Residual offset $\sim 100\text{nV}$, but reduced bandwidth
- Note: input choppers should not be merged!

Dead-Banding



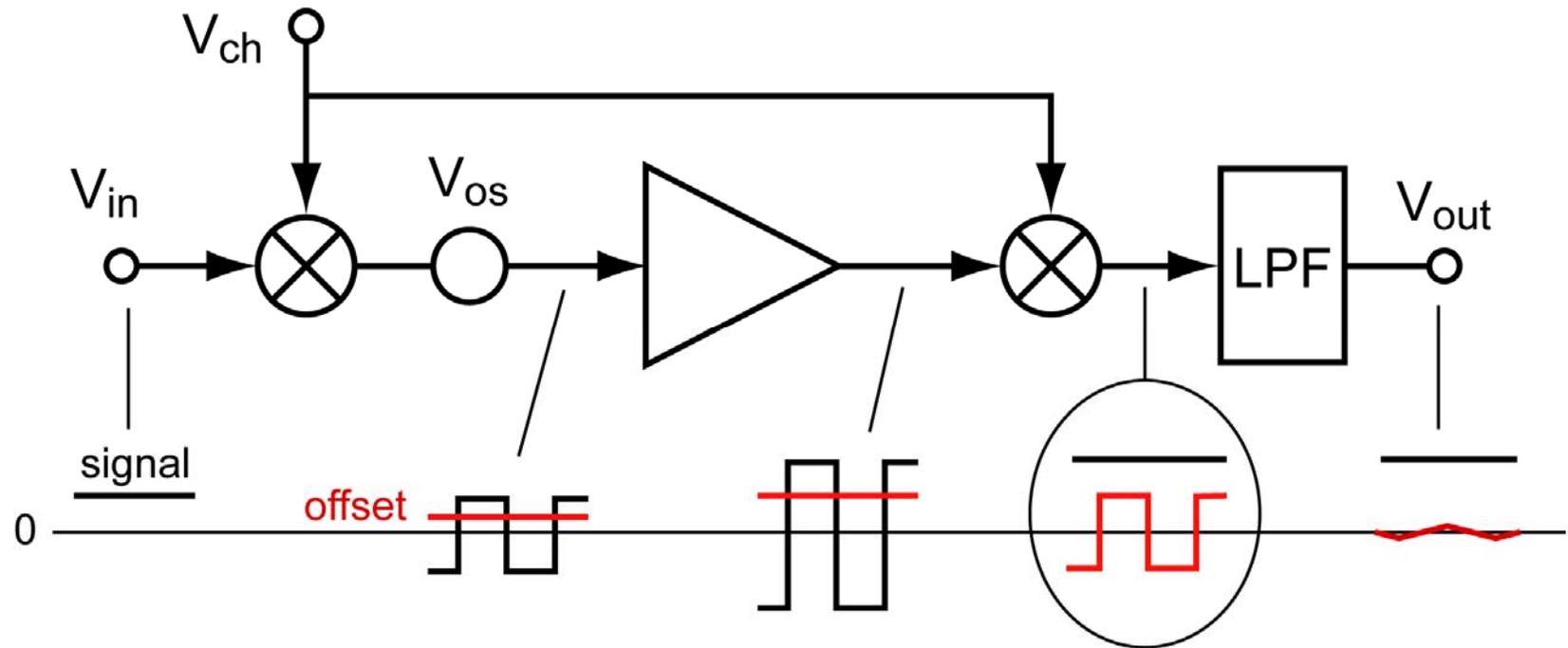
- During dead-band amplifiers output is tri-stated^{26,27,28}
- Residual offset $\sim 200\text{nV}$!
- BUT loss of gain and aliasing due to S&H action
 \Rightarrow slightly worse noise performance

Dealing with Spikes: Overview

- BP Filtering: $\sim 0.5\mu\text{V}$ offset, complex clock timing
- Dead-banding: $\sim 200\text{nV}$ offset, wide BW
- Nested chopping: $\sim 100\text{nV}$ offset, but limited BW

Last two techniques represent best compromise between offset magnitude and circuit complexity

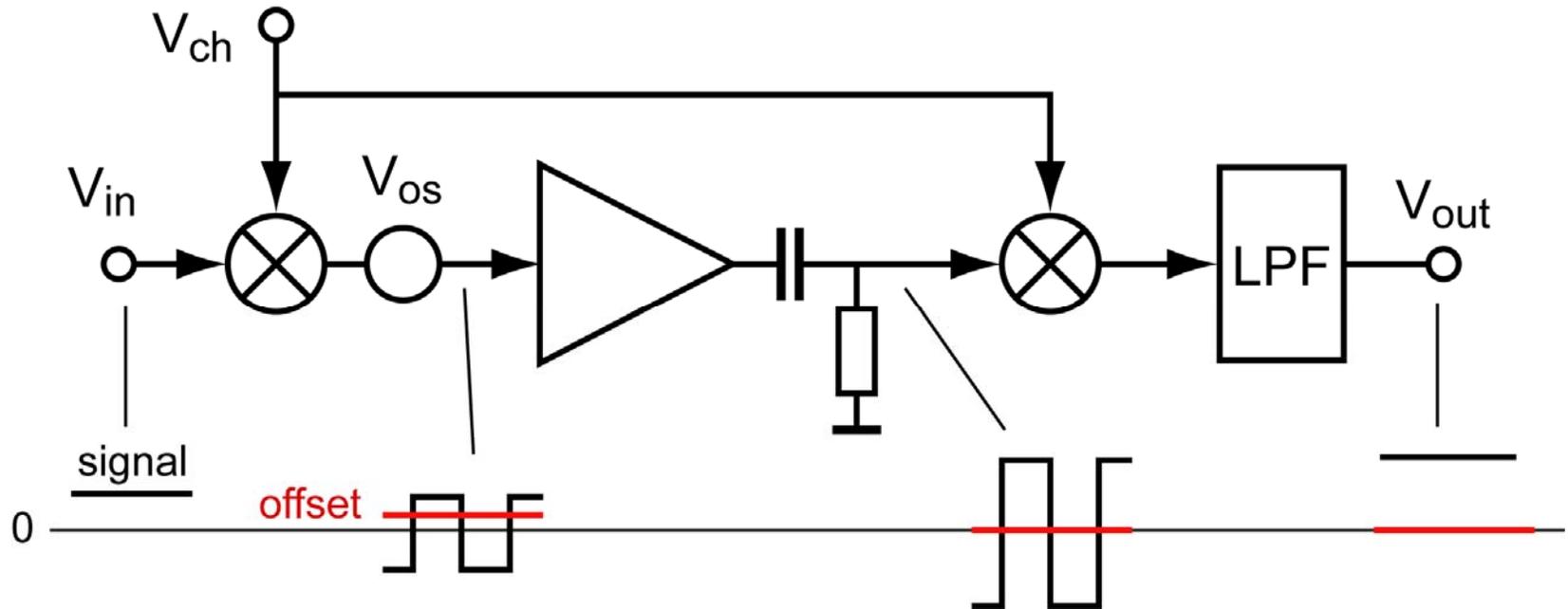
Chopping Artifacts (Ripple)



Modulated offset \Rightarrow chopping artifacts (ripple)

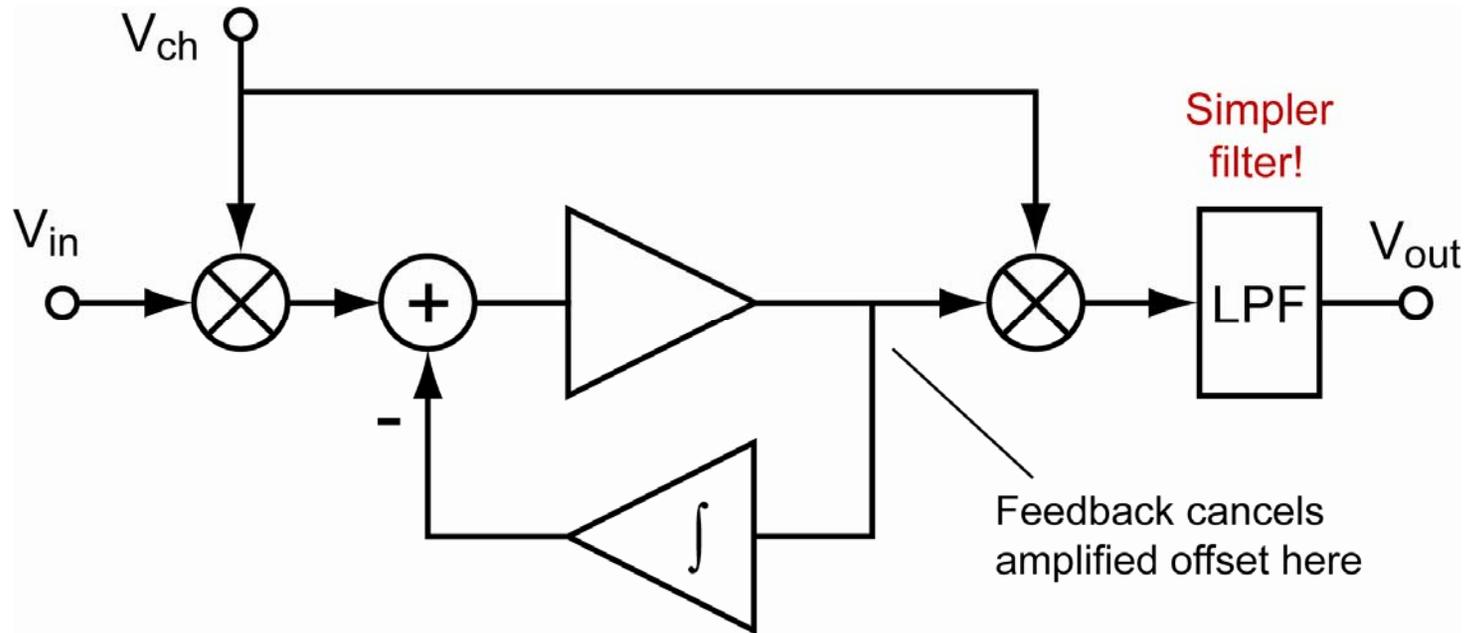
- Can be removed by a low-pass filter
- BUT filter cut-off frequency must be quite low \Rightarrow difficult to realize on chip

AC Coupling



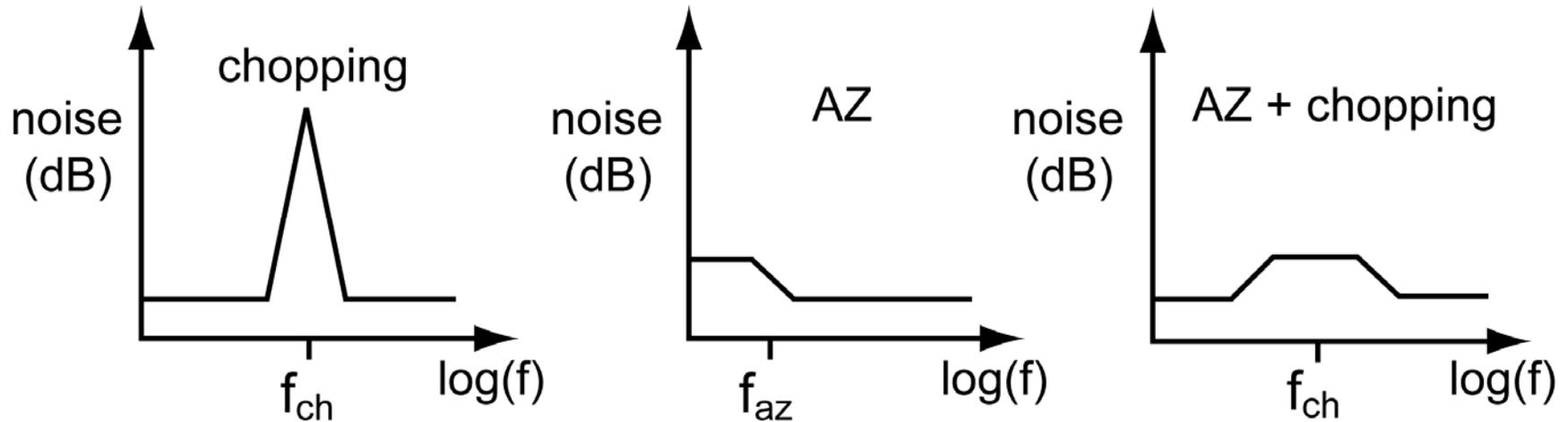
- AC coupling blocks the amplifier's offset
⇒ no output ripple!
- But cut-off frequency must again be quite low

DC Servo Loop



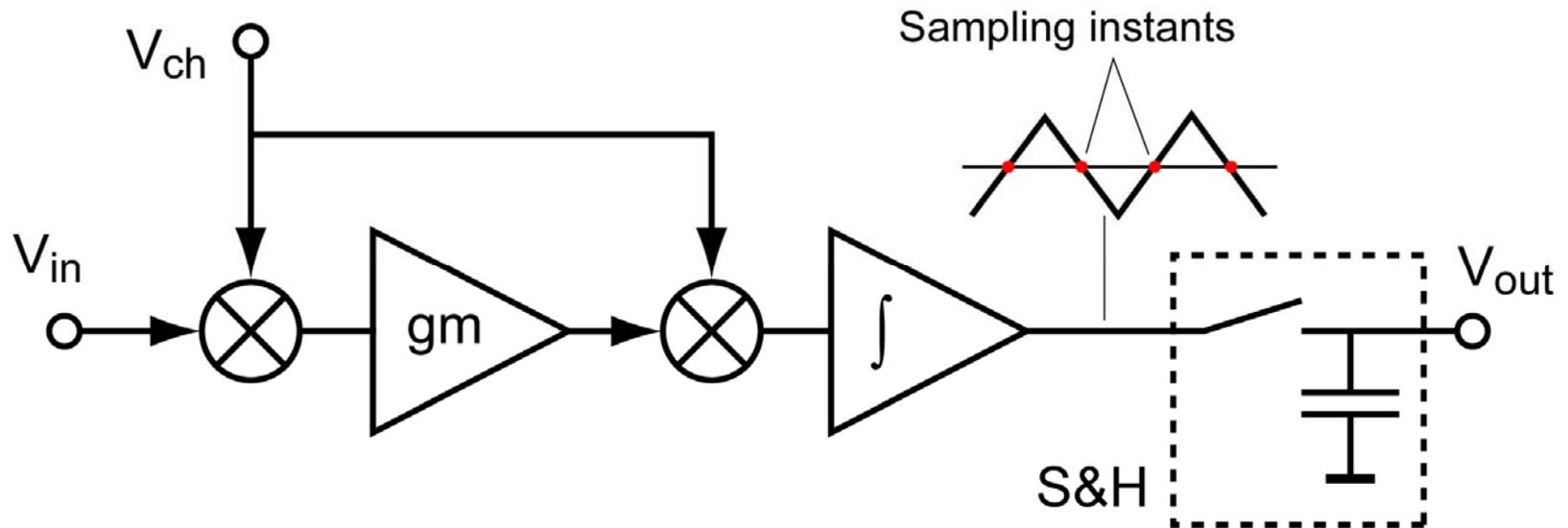
- DC “servo” loop suppress the amplifier’s offset^{34,35}
- Integrator is not in the main signal path
⇒ much easier to realize a low cut-off frequency
- Residual ripple can be removed by a simple LPF

Auto-zeroing and Chopping



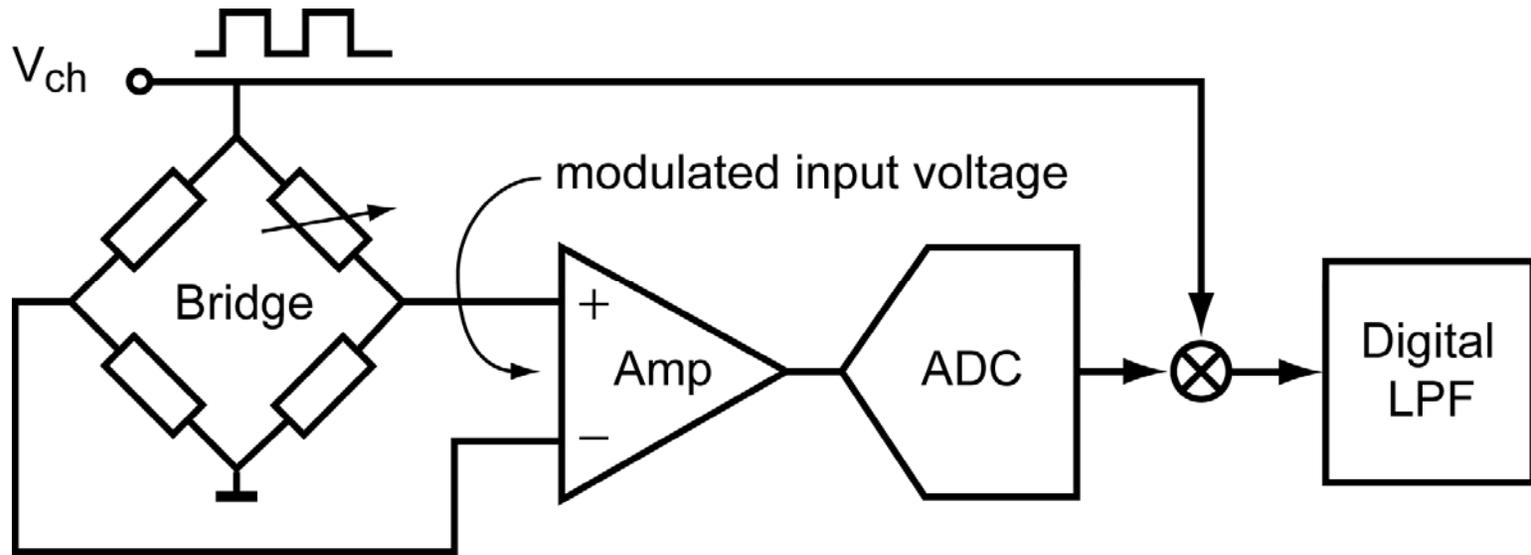
- Compared to standard AZ, significantly improves LF noise performance^{30,31,32,33}
- Much less ripple than with chopping alone
- Choosing $f_{ch} = 2f_{az} \Rightarrow$ residual offset of auto-zeroing is exactly averaged \Rightarrow aliased noise has notch at DC

Switched Capacitor Filter



- Chopped offset is integrated & the triangular ripple is then sampled at the zero-crossings^{9,37,38}
- SC filter essentially eliminates residual ripple
- Filter introduces delay and a (small) noise penalty

Digital Filtering



- Chopped signal is digitized
- Demodulation is done digitally^{31,39}
- Chopper artifacts are removed by a digital LPF e.g. a sinc filter with notches at f_{ch}

Dealing with Artifacts: Overview

Reduce the amplifier's initial offset

- Auto-zeroing and chopping: increased noise
- DC servo: still requires some analog filtering
- Switched capacitor filtering

Digital Filtering

- Very low cut-off frequencies can be realized
- Decimation filter of a $\Sigma\Delta$ ADC can be used to remove chopper artifacts \Rightarrow no extra overhead

Chopping: Summary

- Offsets in the range of 50nV-10 μ V can be achieved
- Timing skew limits offset reduction to about 60dB
- Fundamental loss of bandwidth (unless offset-stabilized topologies can be used)
- Eliminates $1/f$ noise, noise floor set by thermal noise
- DOC technique of choice when noise or offset performance is paramount e.g. in biomedical amplifiers, low-power opamps, smart sensors etc.

Some Caveats

- Chopping and auto-zeroing rely on amplifier linearity
- Amplifier non-linearity will result in a residual offset!
- Presence of timing jitter \Rightarrow variable settling (AZ) or non-50% duty-cycles (chopping) \Rightarrow voltage noise
- Finite switch resistance \Rightarrow trade-off between CI, thermal noise and BW limitations

Summary

- Offset and $1/f$ are part of life!
- Trimming
 - reduces offset but not $1/f$ noise
 - simple, no loss of bandwidth
- Auto-zeroing
 - eliminates $1/f$ noise, but noise aliasing \Rightarrow LF noise
 - Auto-zero period \Rightarrow Loss of bandwidth
 - CT operation \Rightarrow OS and Ping-pong topologies
- Chopping
 - eliminates $1/f$ noise \Rightarrow best noise efficiency
 - LPF \Rightarrow loss of bandwidth (unless OS is used)
- Nested DOC techniques \Rightarrow sub-microvolt offset